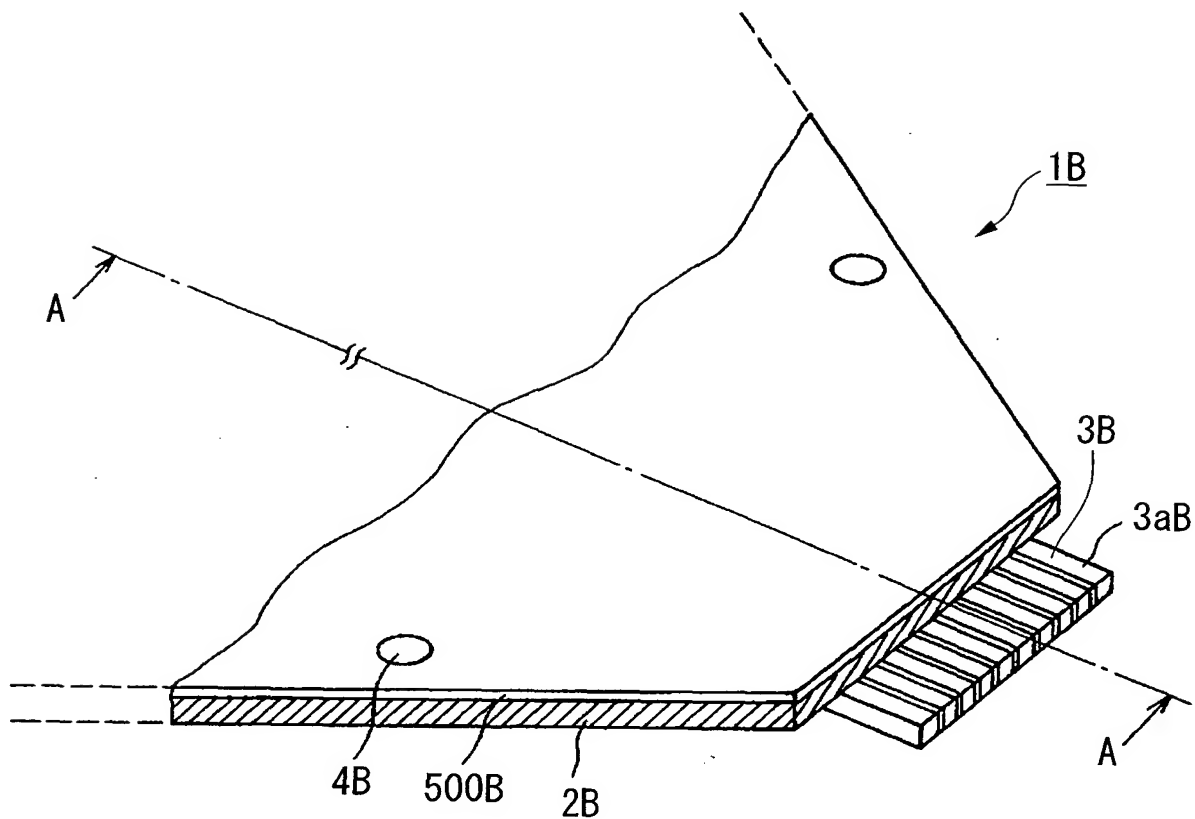
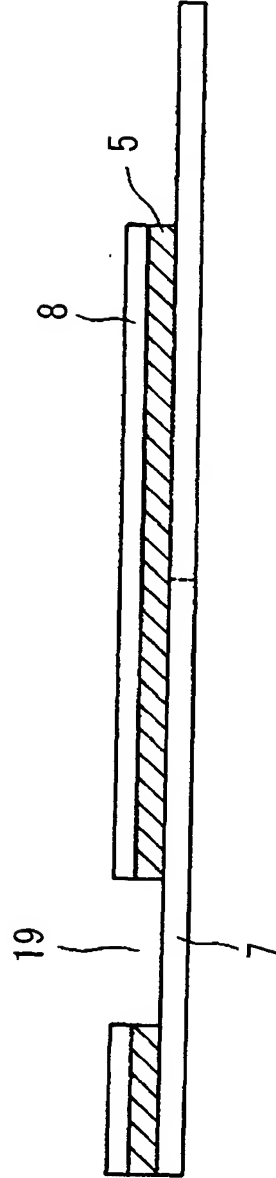


FIG. 1



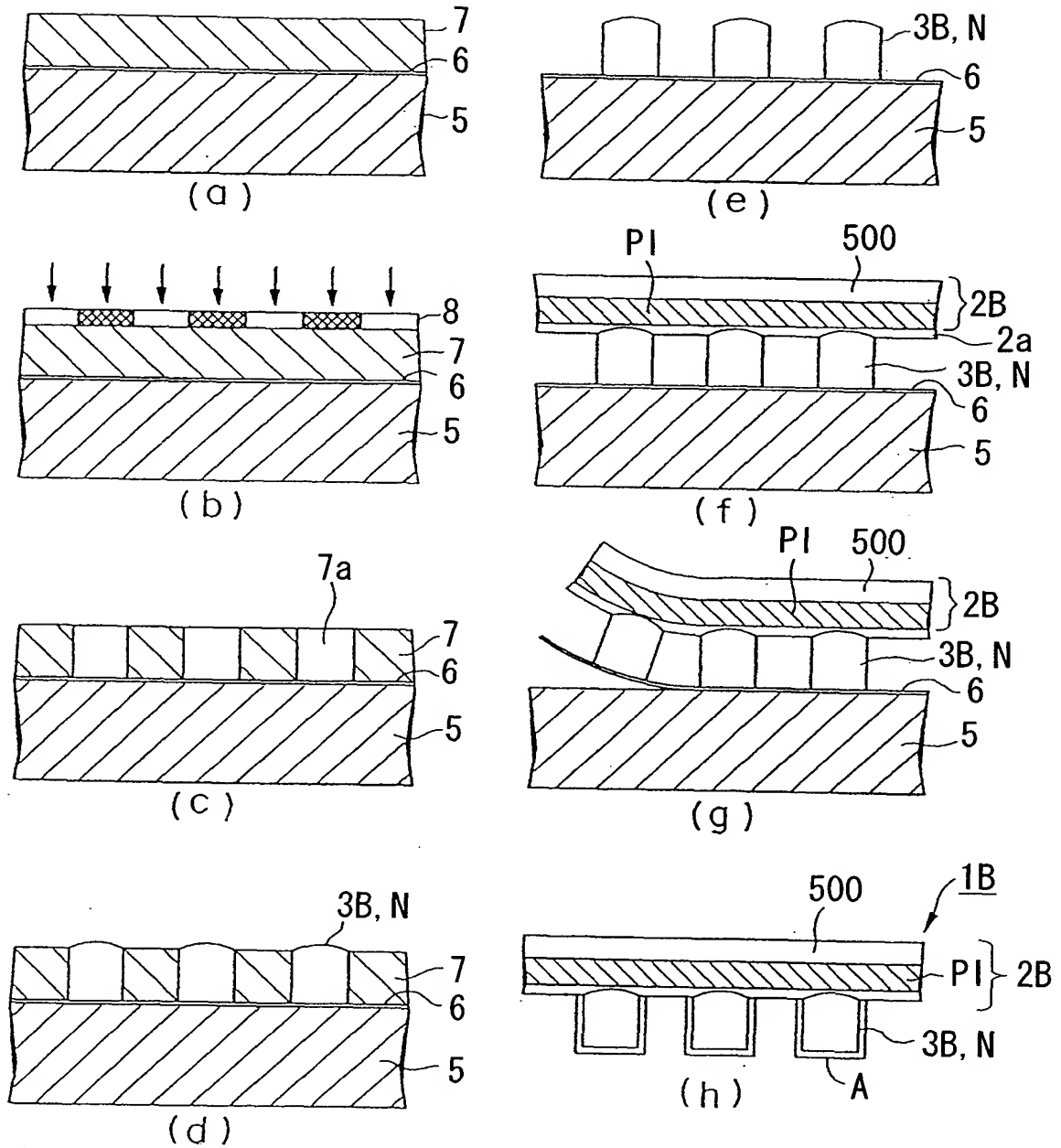
10076508-061902

FIG. 2



206T90" 8059/00F

FIG. 3



10076508-061902

FIG. 4

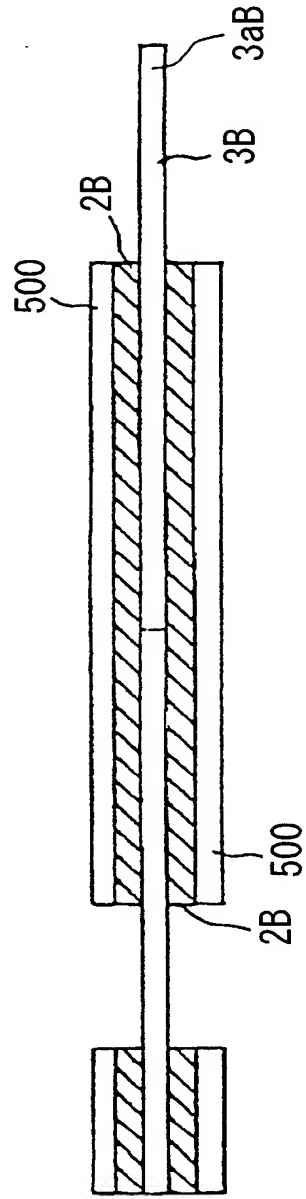


FIG. 5

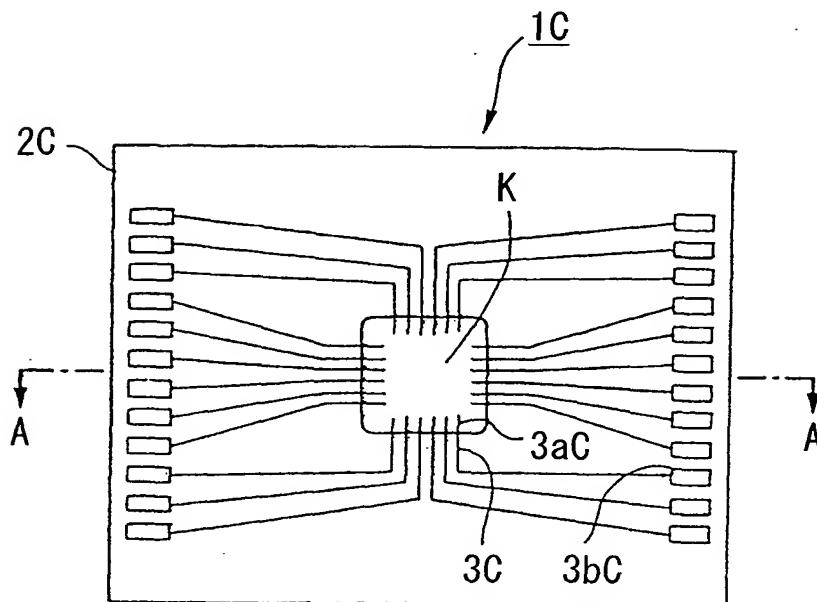


FIG. 6

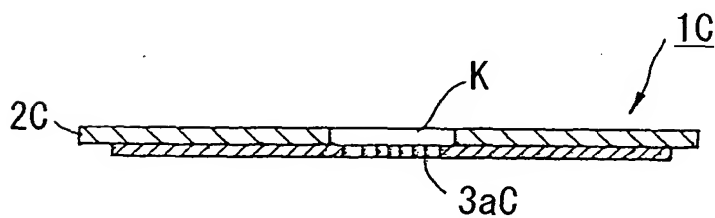


FIG. 7

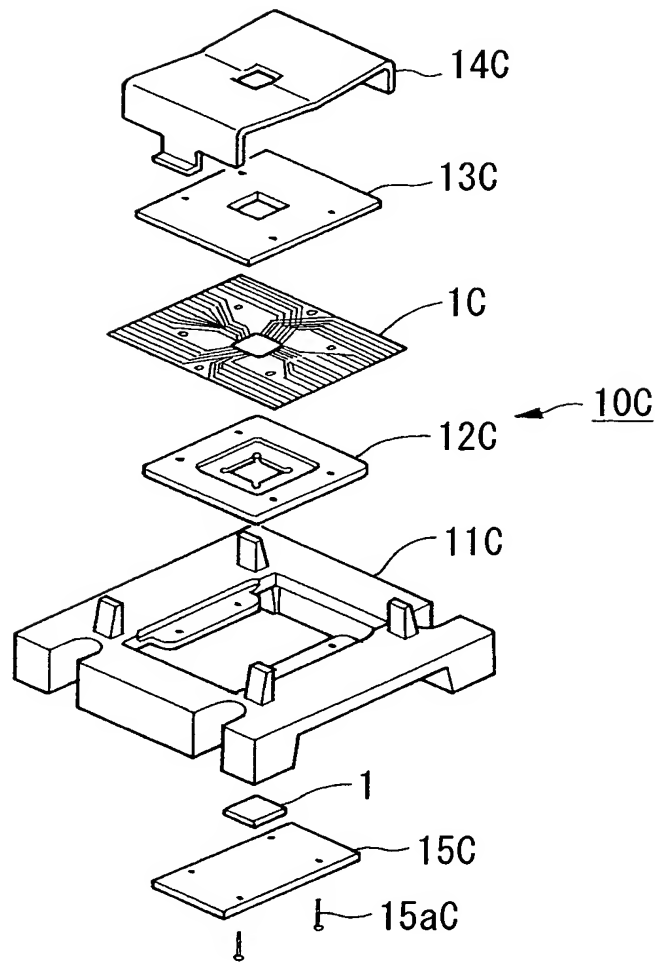


FIG. 8

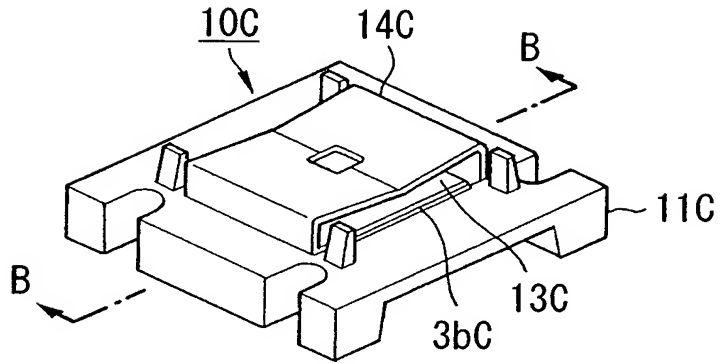
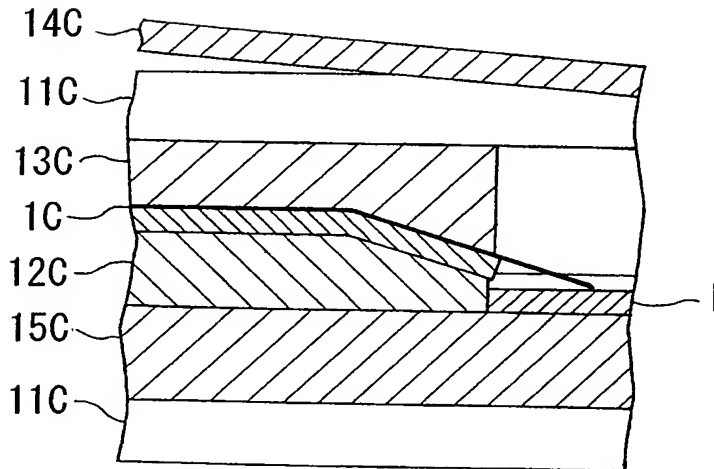


FIG. 9



10076508.06190

FIG. 10

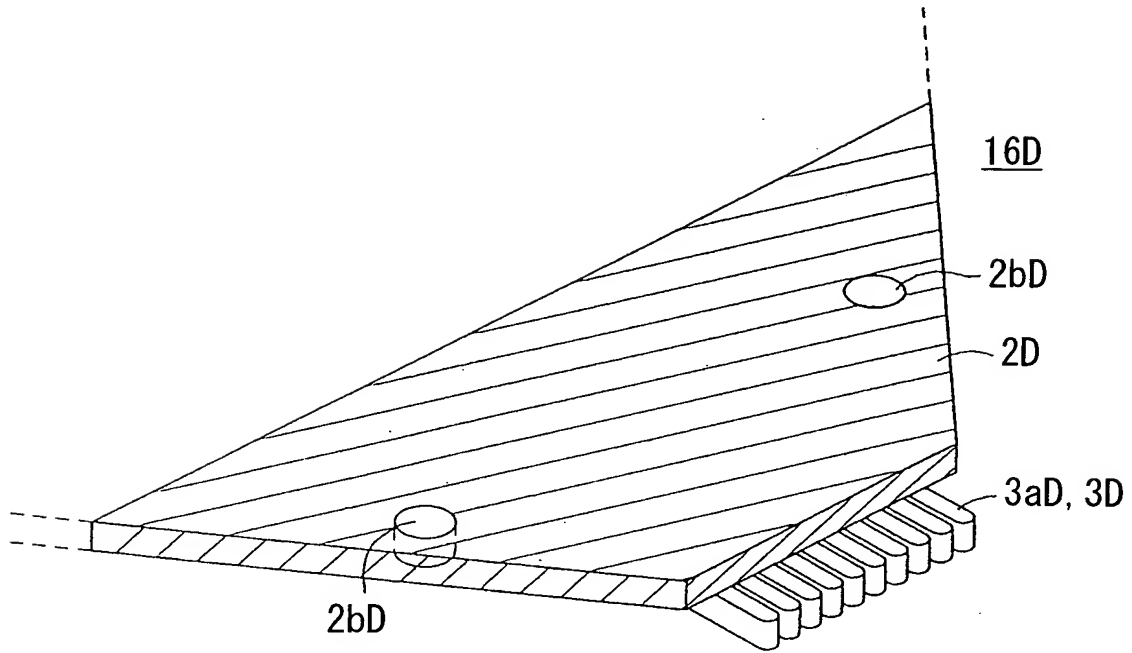




FIG. 11

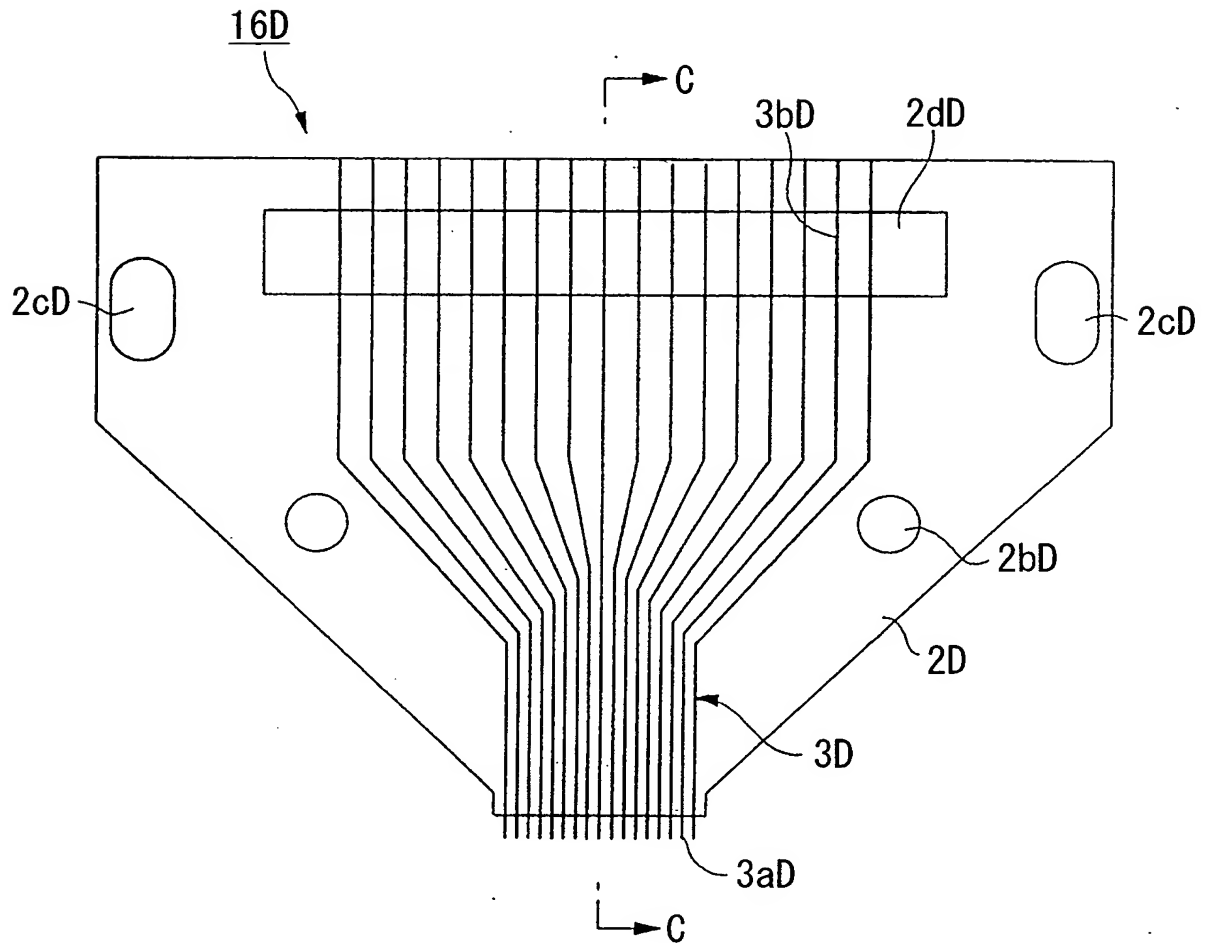


FIG. 12

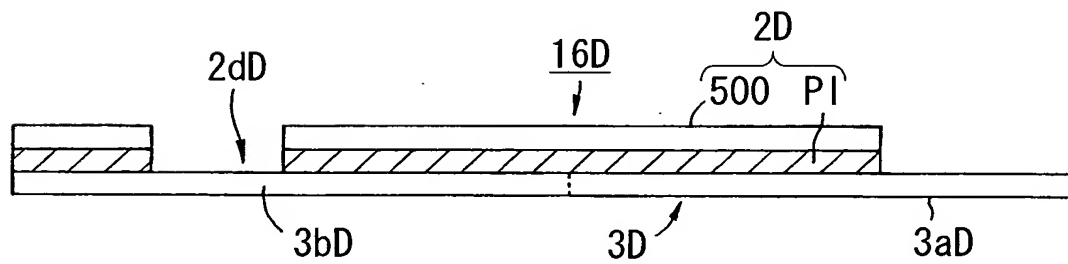
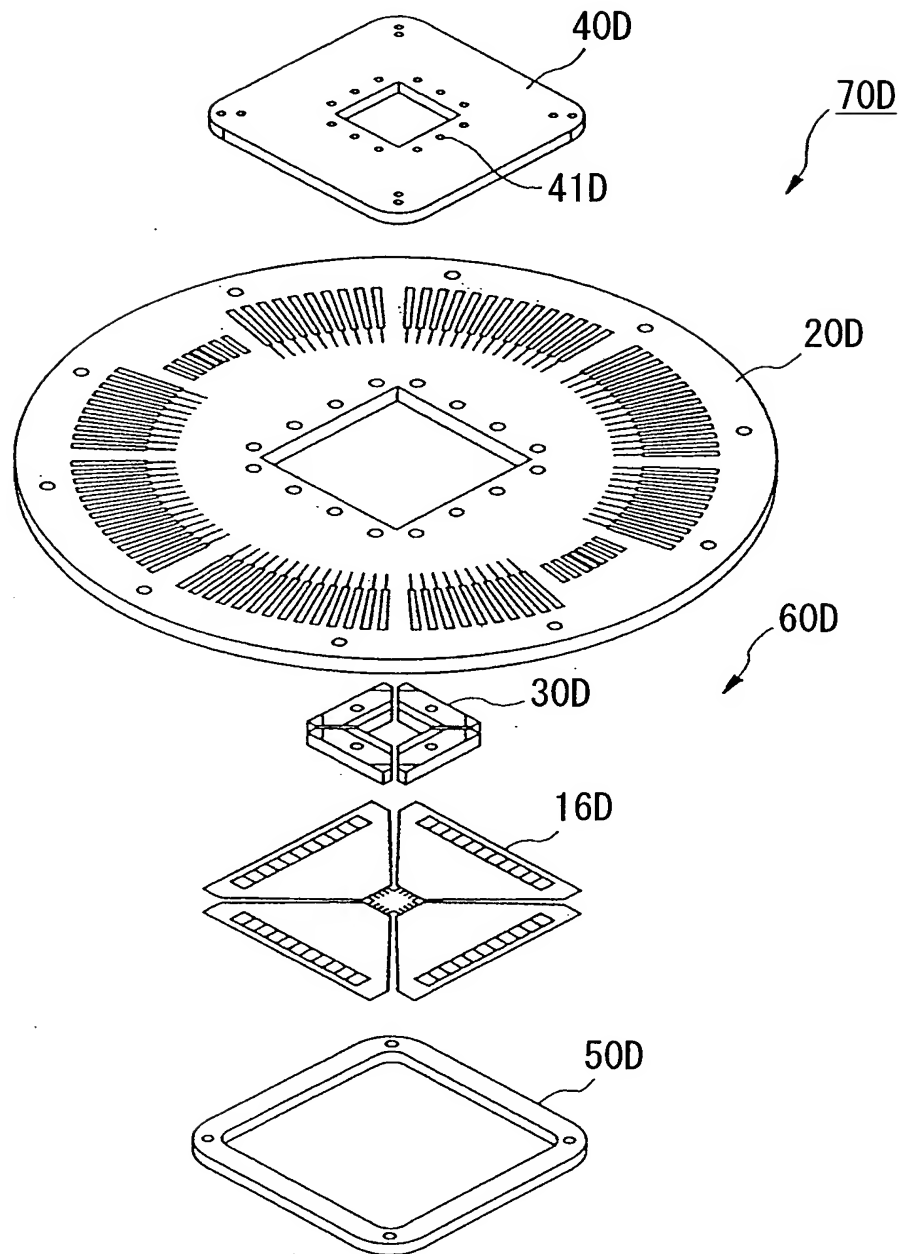


FIG. 13



206T90-8059Z00T

FIG. 14

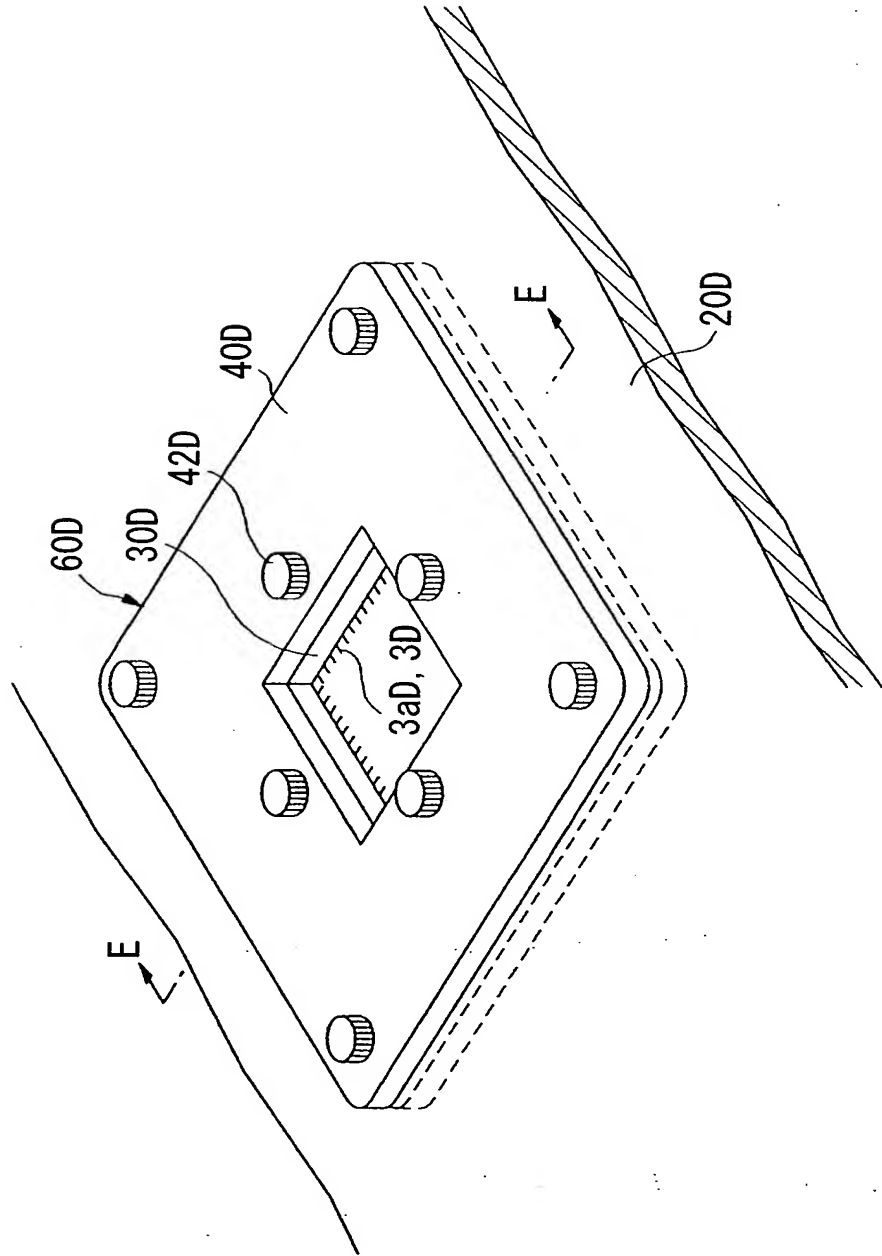


FIG. 15

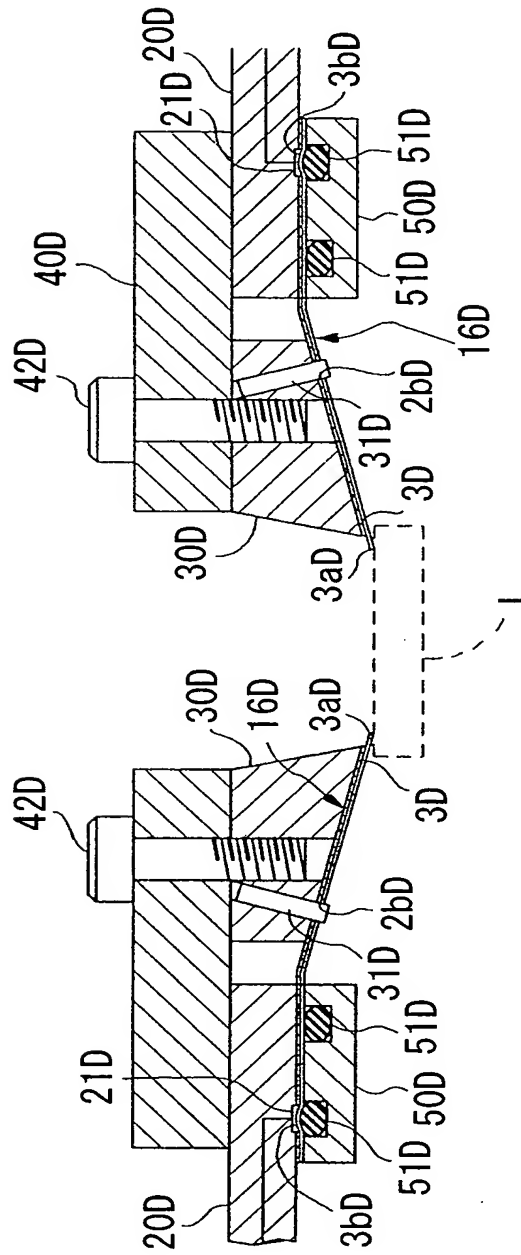


FIG. 16

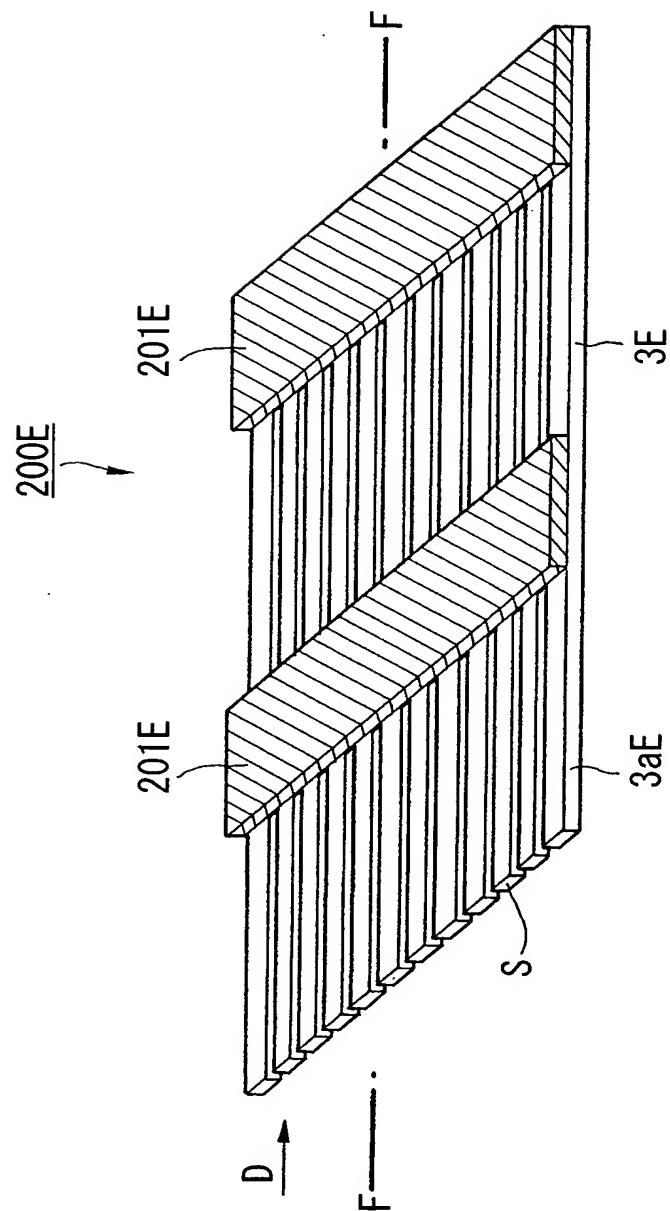
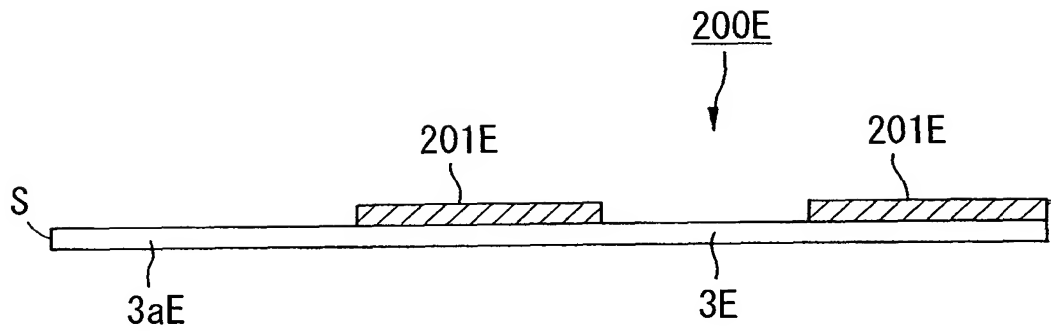
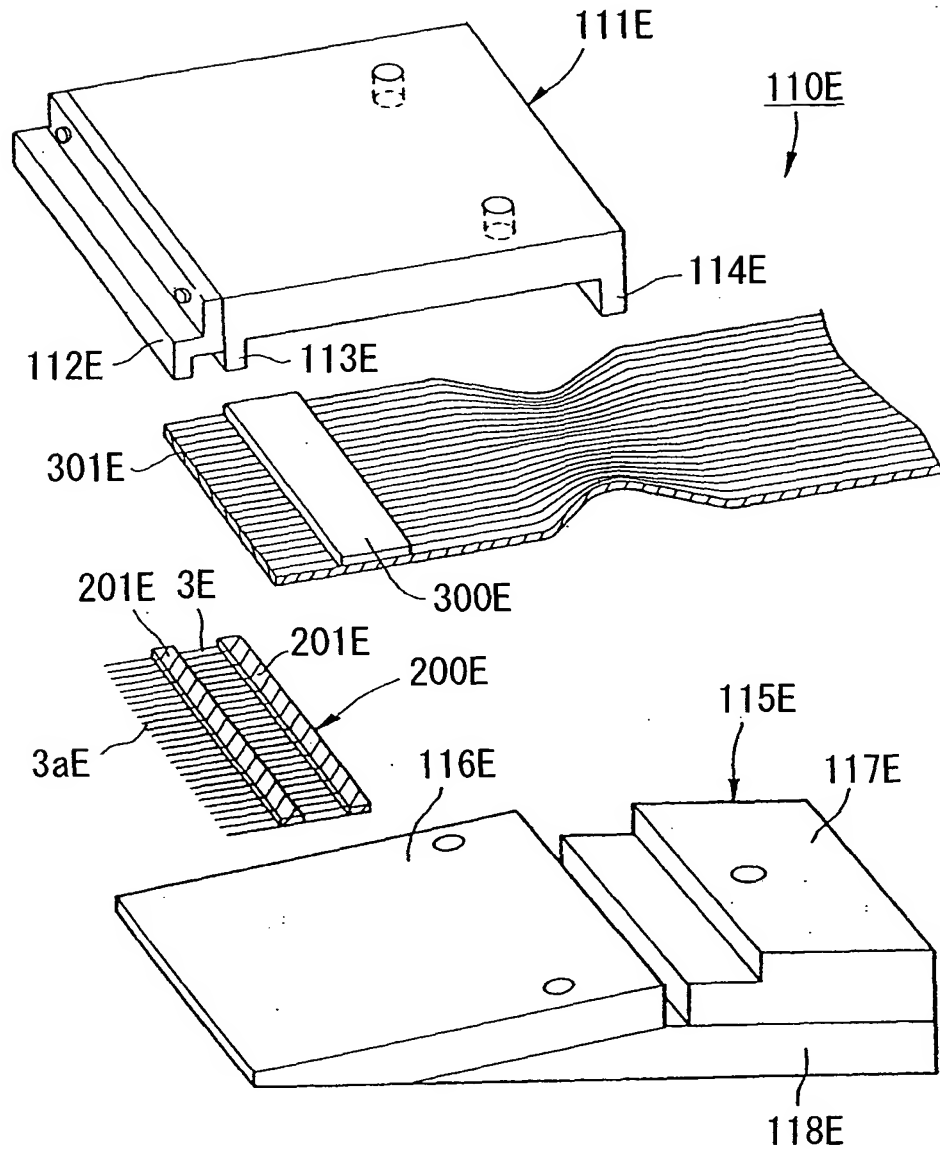


FIG. 17



10076508-051902

FIG. 18



10076508-061902

FIG. 19

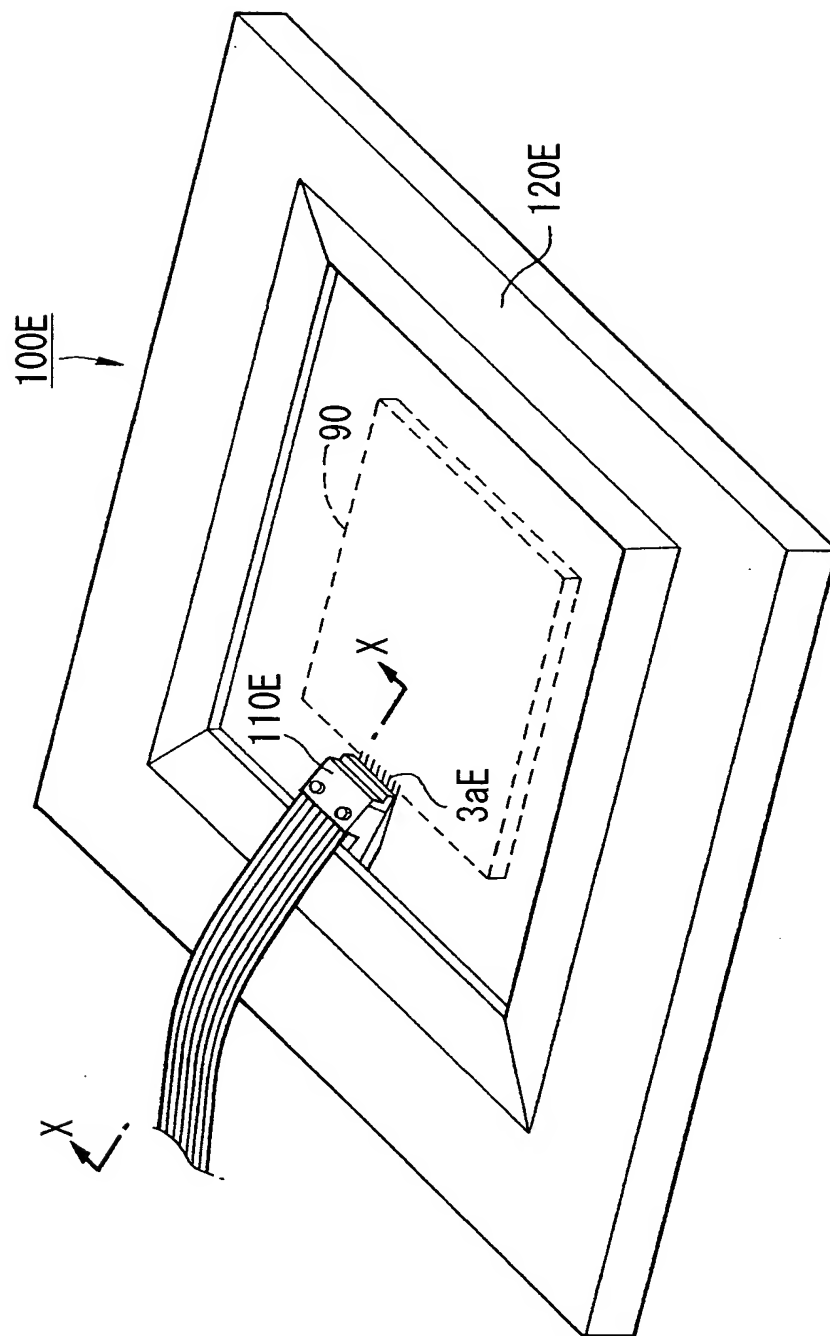




FIG. 20

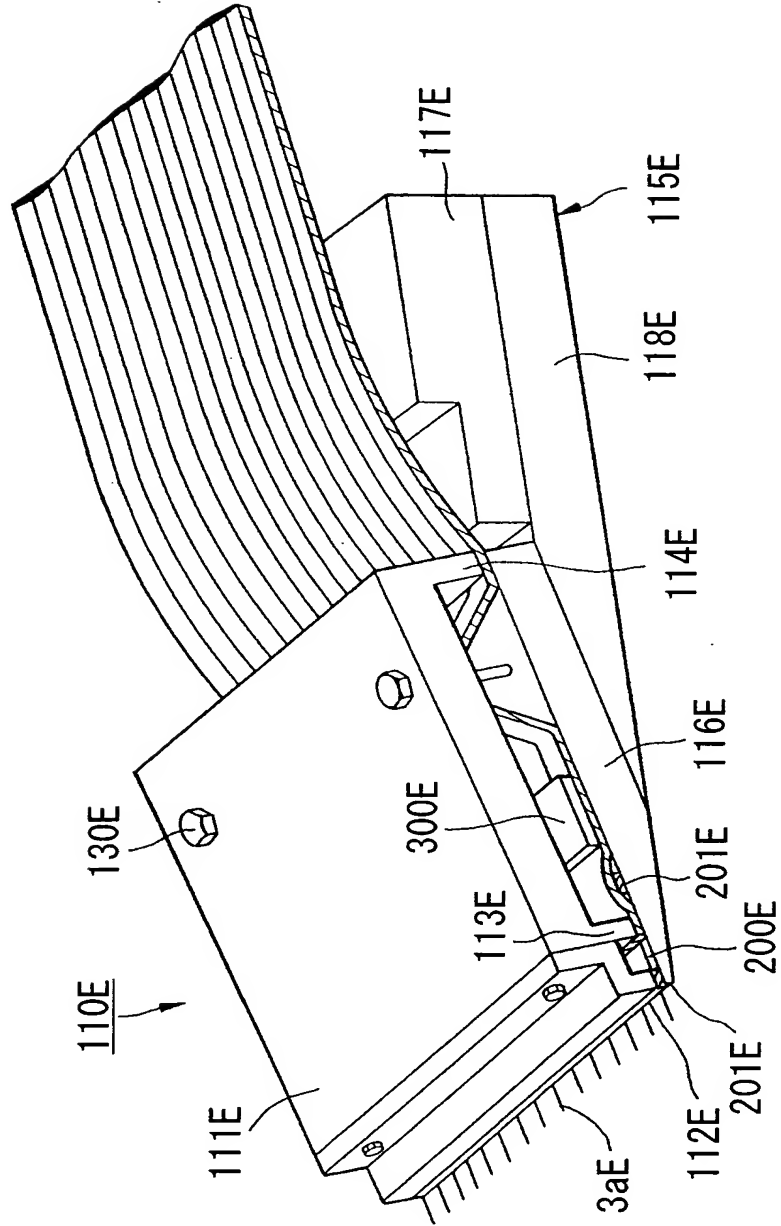


FIG. 21

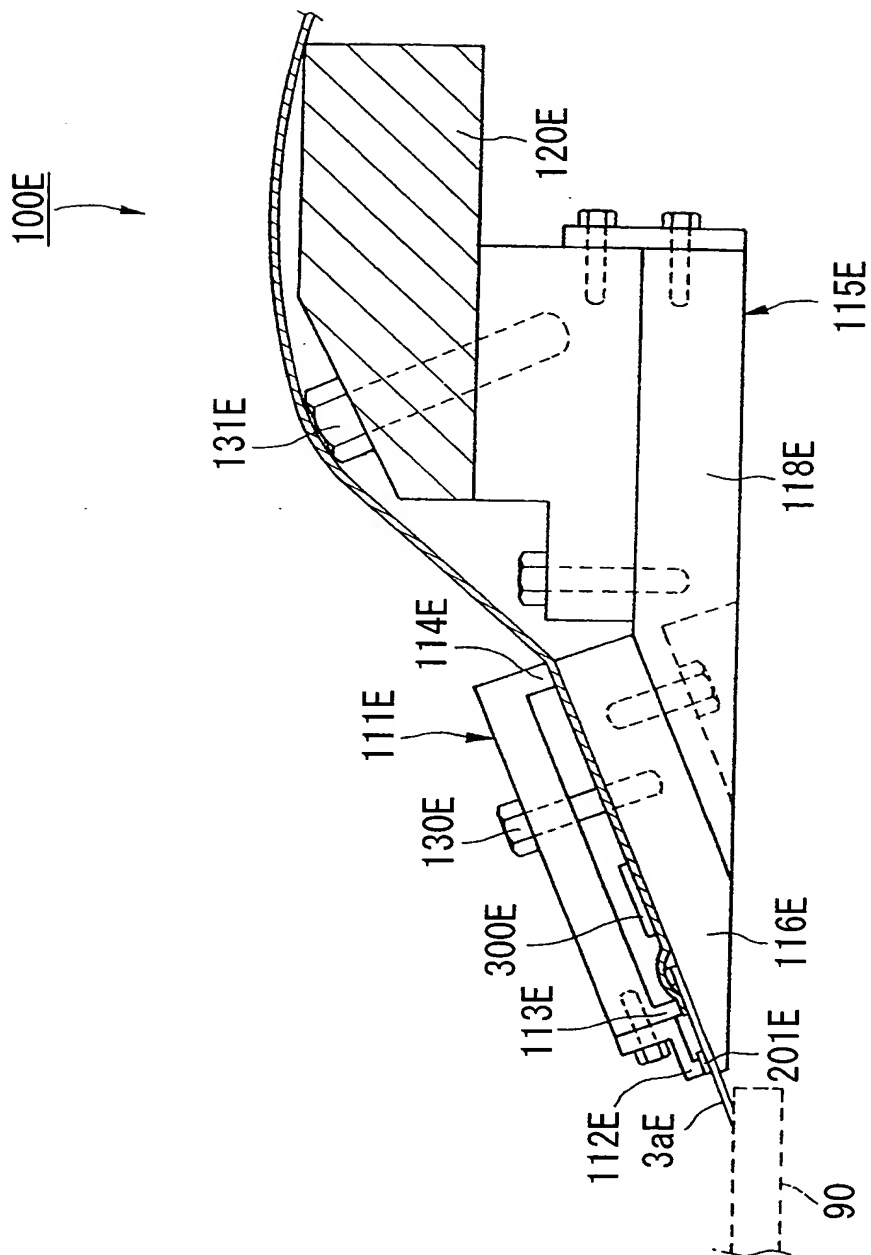


FIG. 22

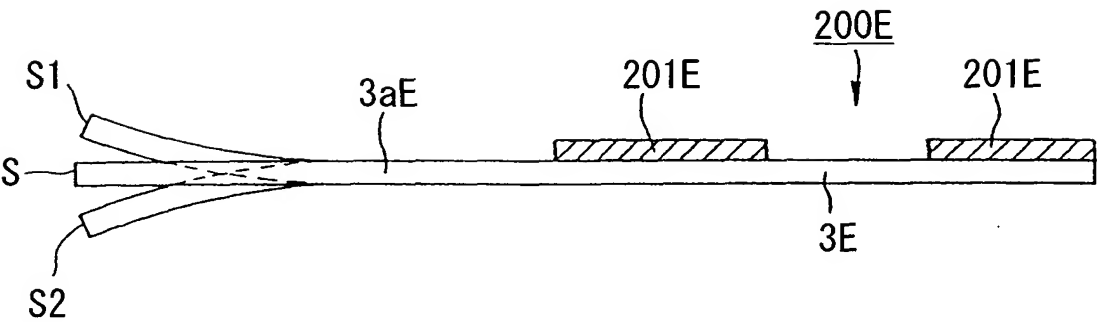


FIG. 23

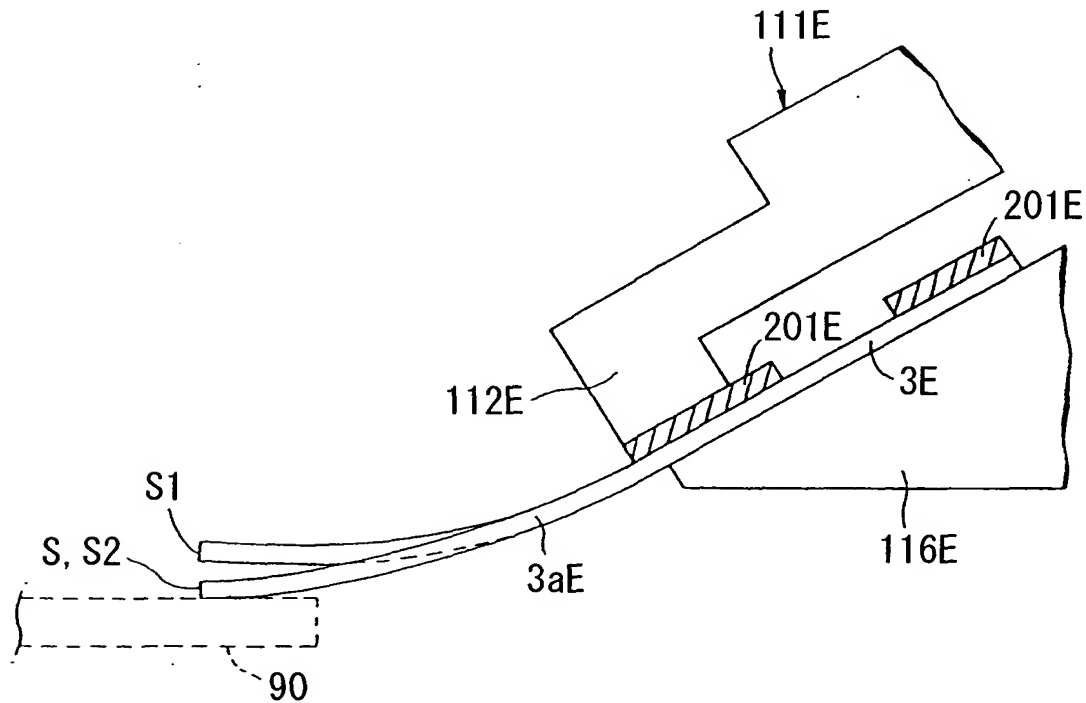


FIG. 24

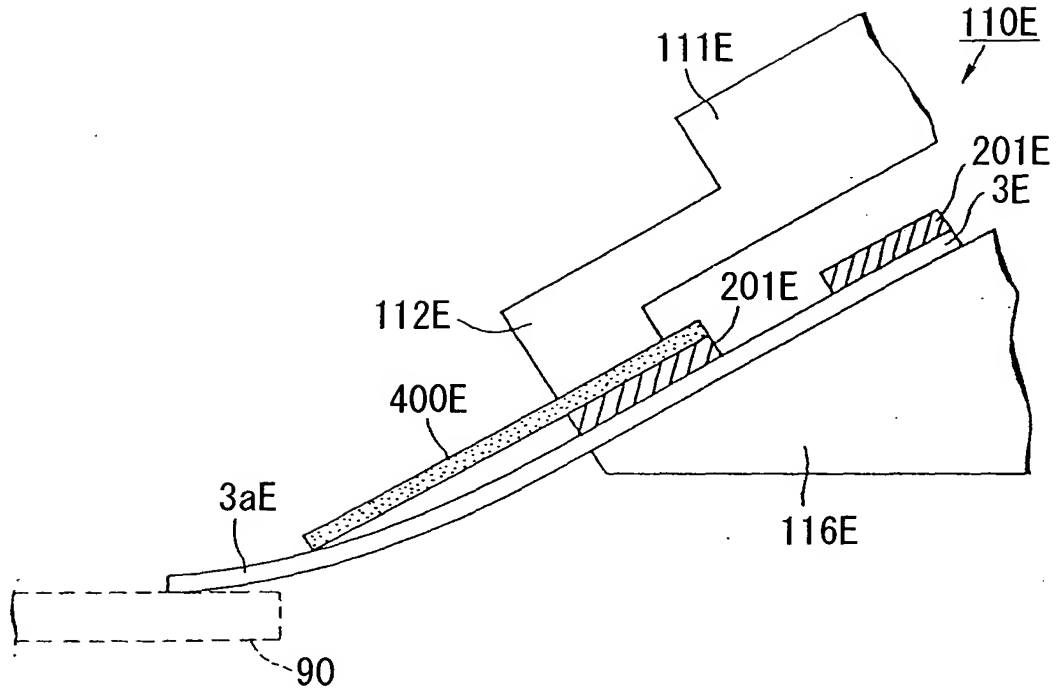


FIG. 25

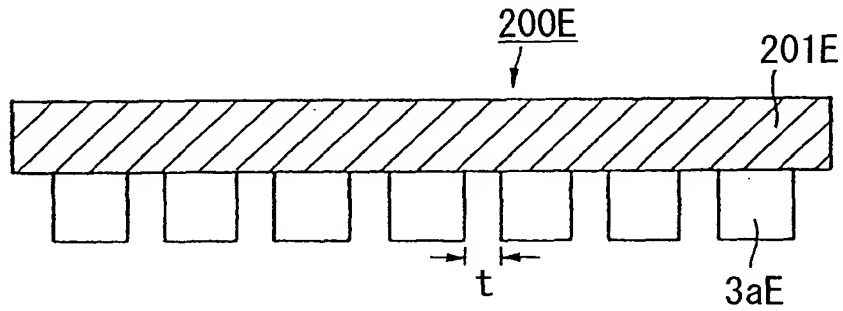


FIG. 26

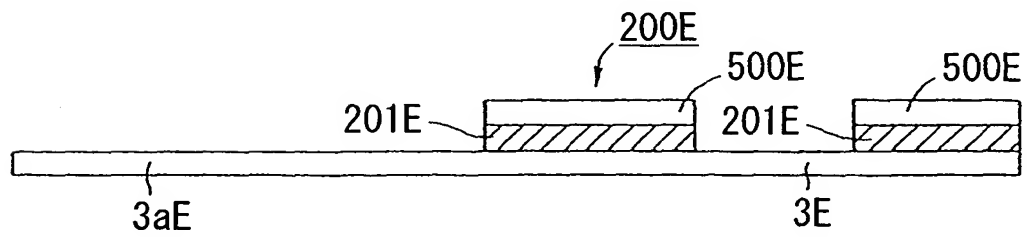


FIG. 27

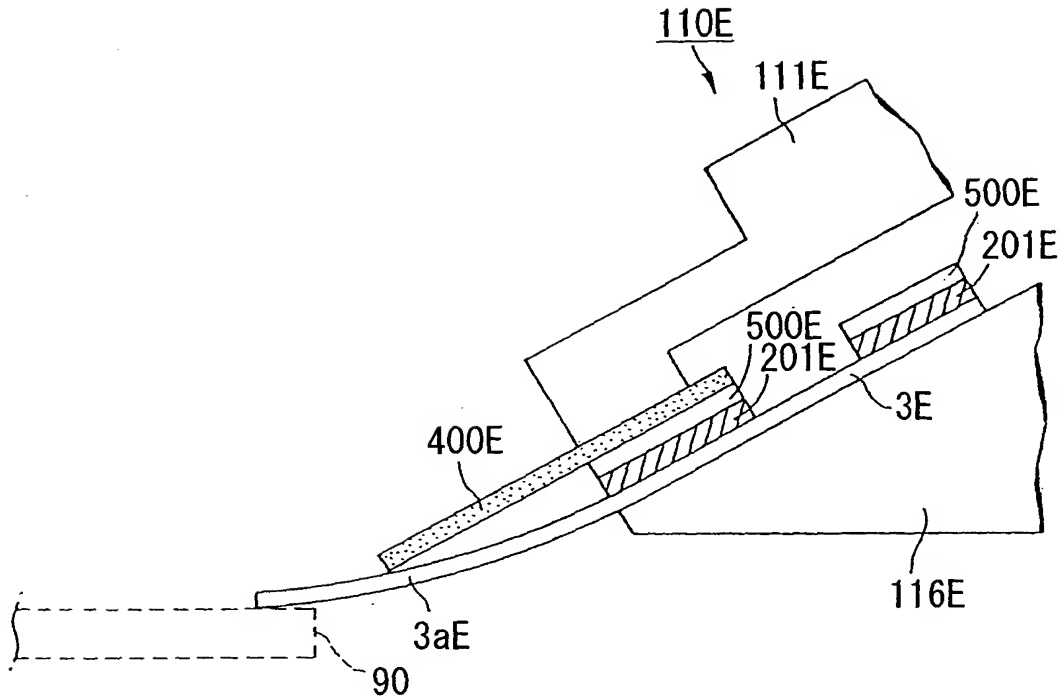


FIG. 28

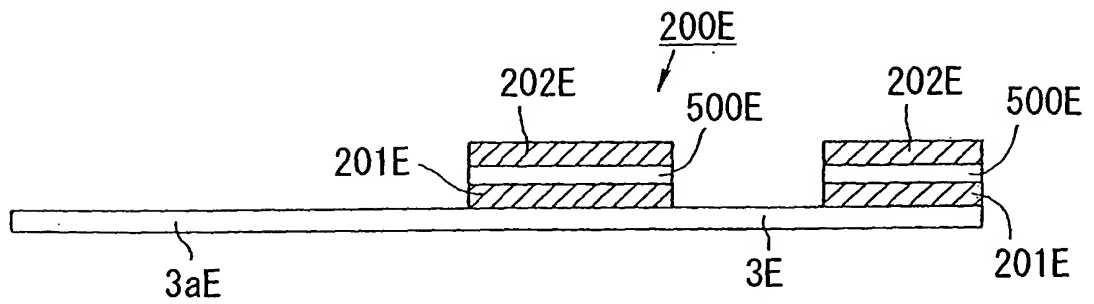


FIG.29

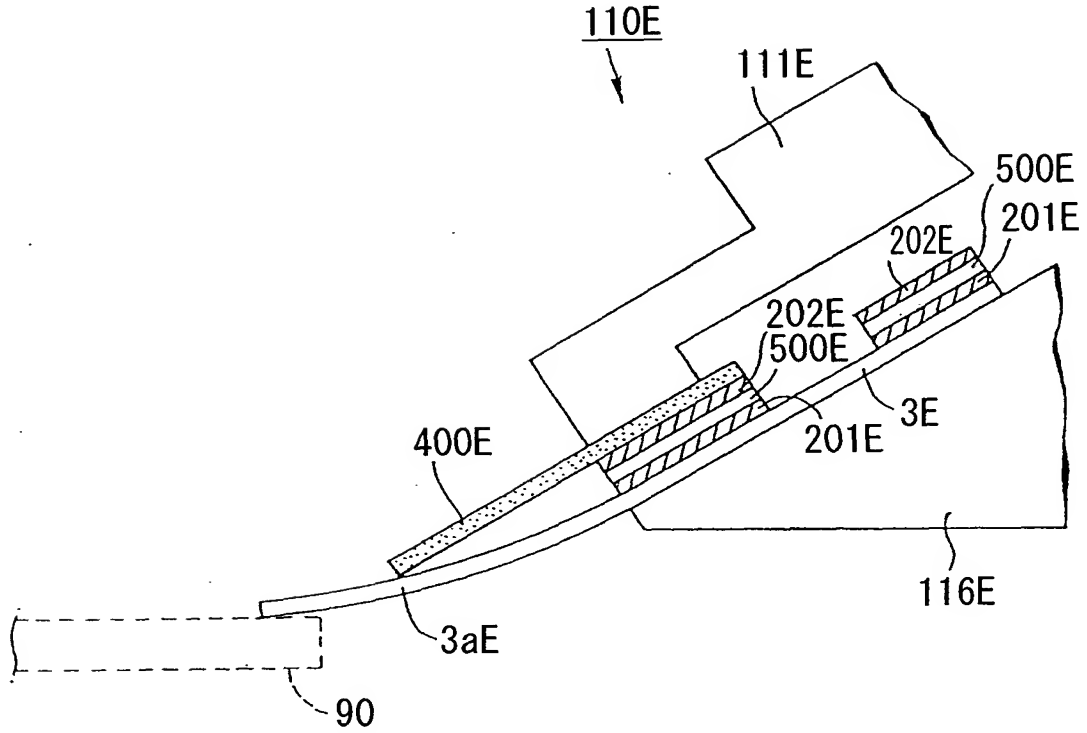


FIG. 30

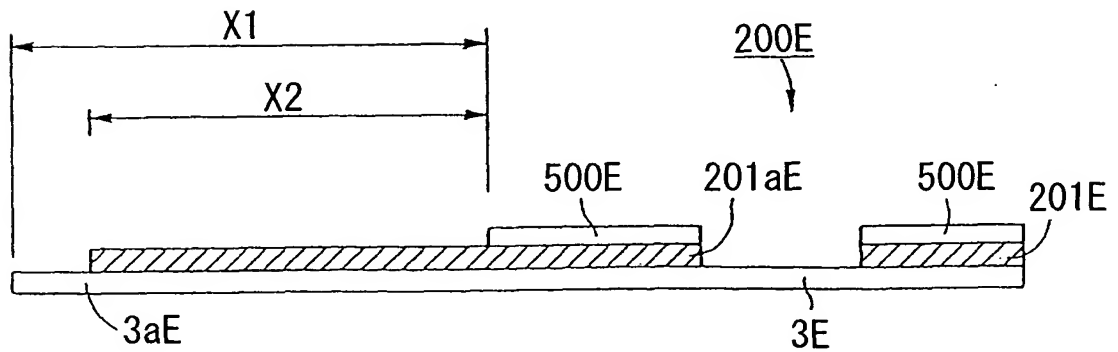
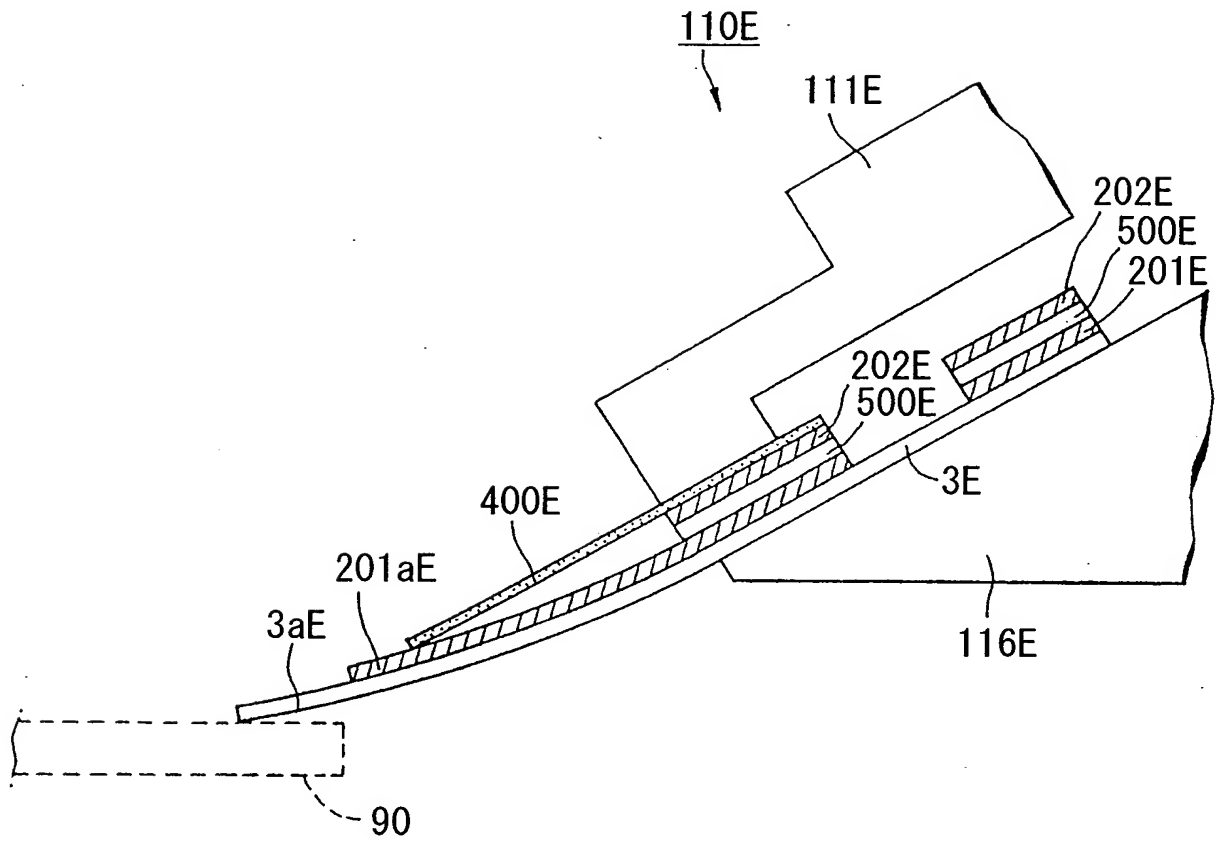


FIG. 10 is a cross-sectional view of a second embodiment of the device. It shows a substrate 110E with a layer 111E. A curved layer 3aE is positioned below 111E. A layer 201aE is on top of 3aE. A layer 400E is on top of 201aE. A layer 500E is on top of 400E. A layer 201E is on top of 500E. A layer 116E is on top of 201E. A dashed line 90 is at the bottom left.

FIG. 33



1005508-061902



FIG. 34

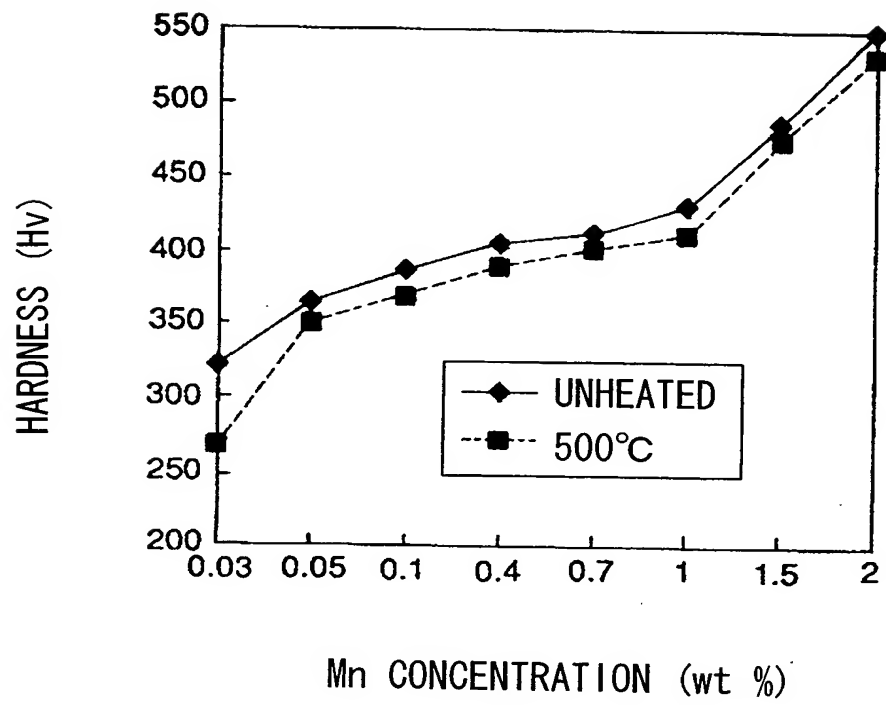
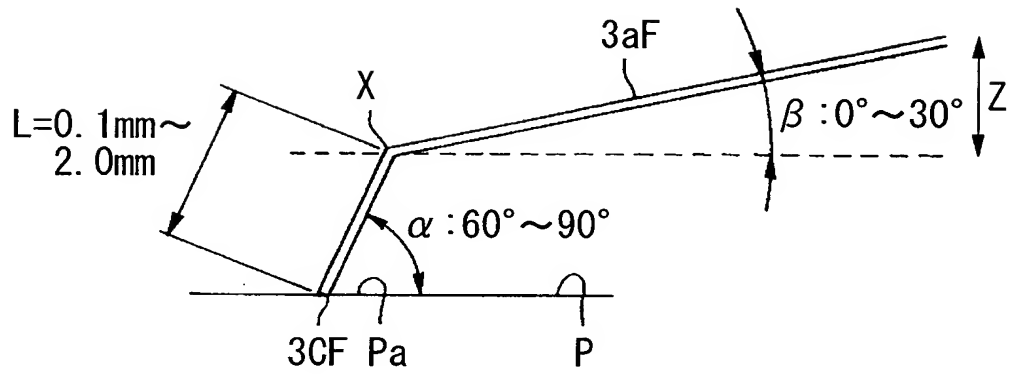
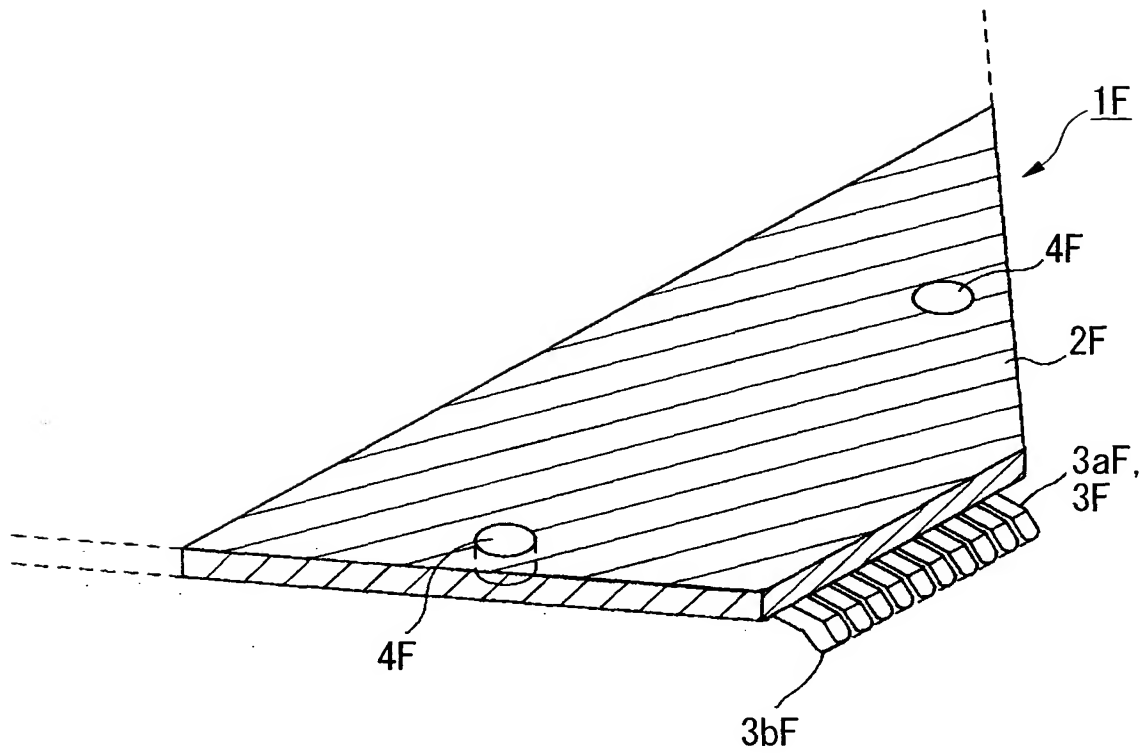


FIG. 35



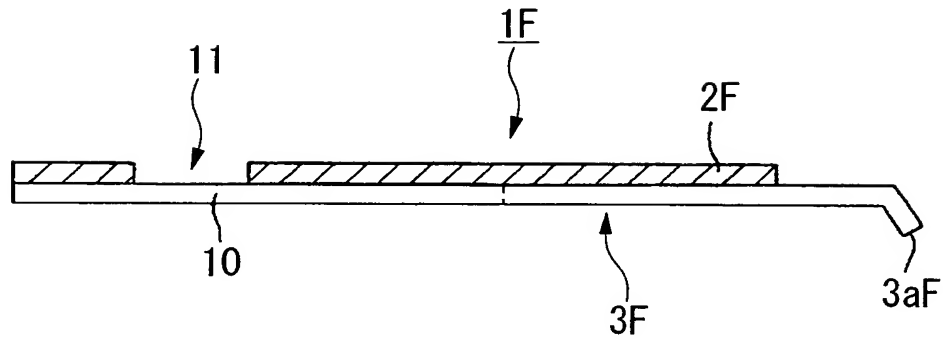
10076508-061902

FIG. 36



10076508-061902

FIG. 37



10076508-061902

[illegible]

FIG. 39

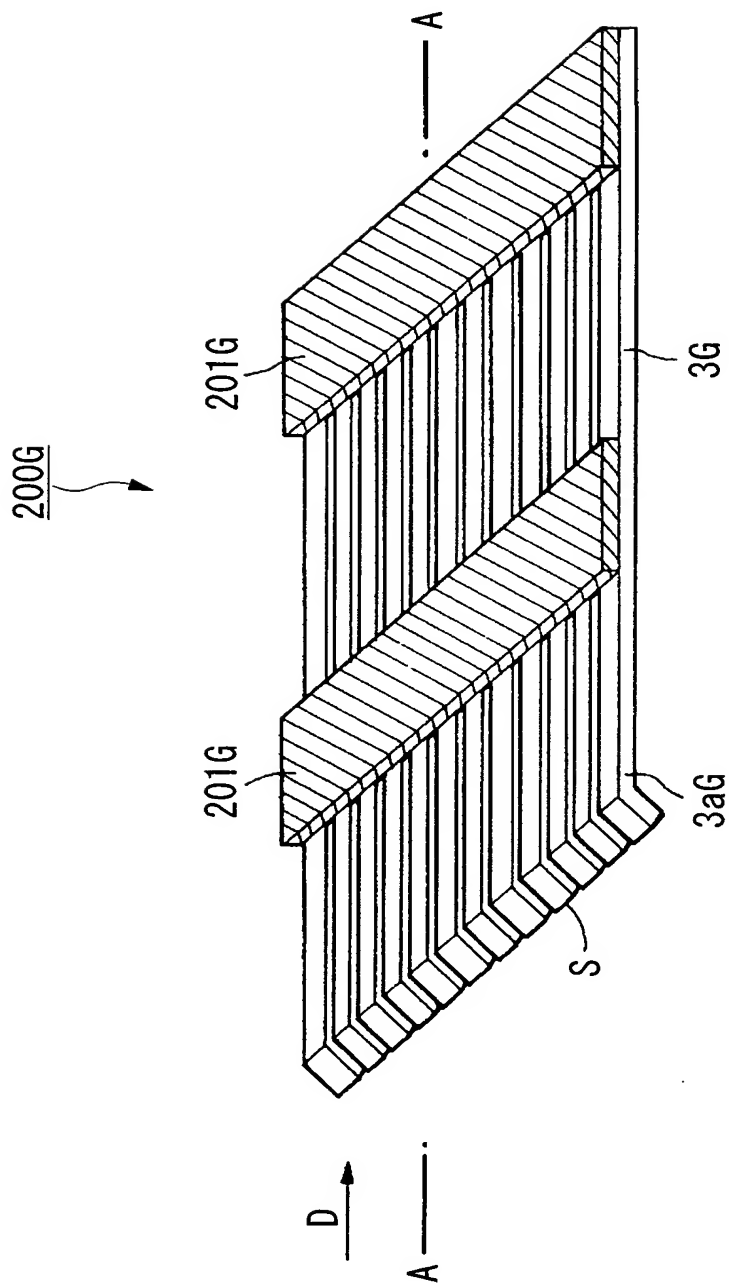
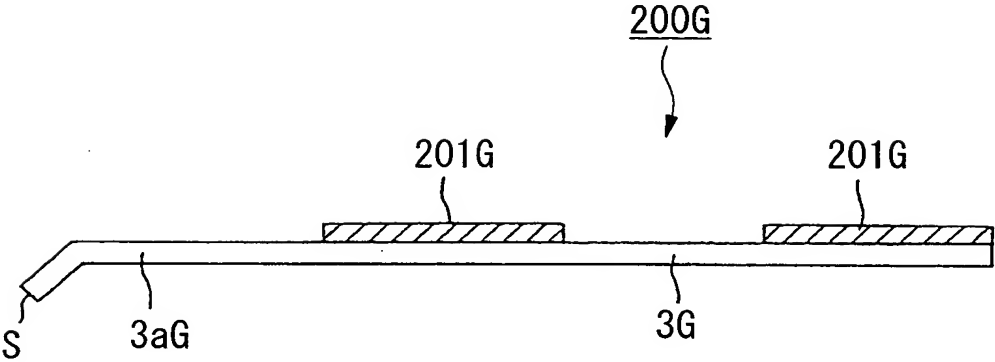


FIG. 40



10076508 "051902  
2006T50" 8059/001

FIG. 41

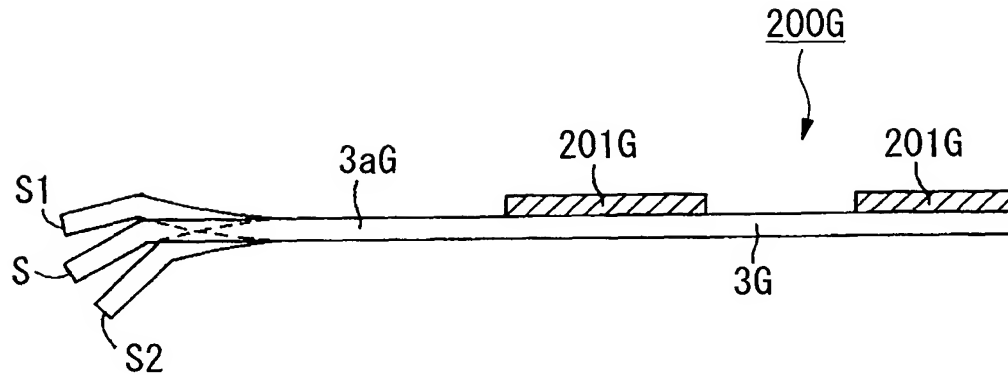


FIG. 42

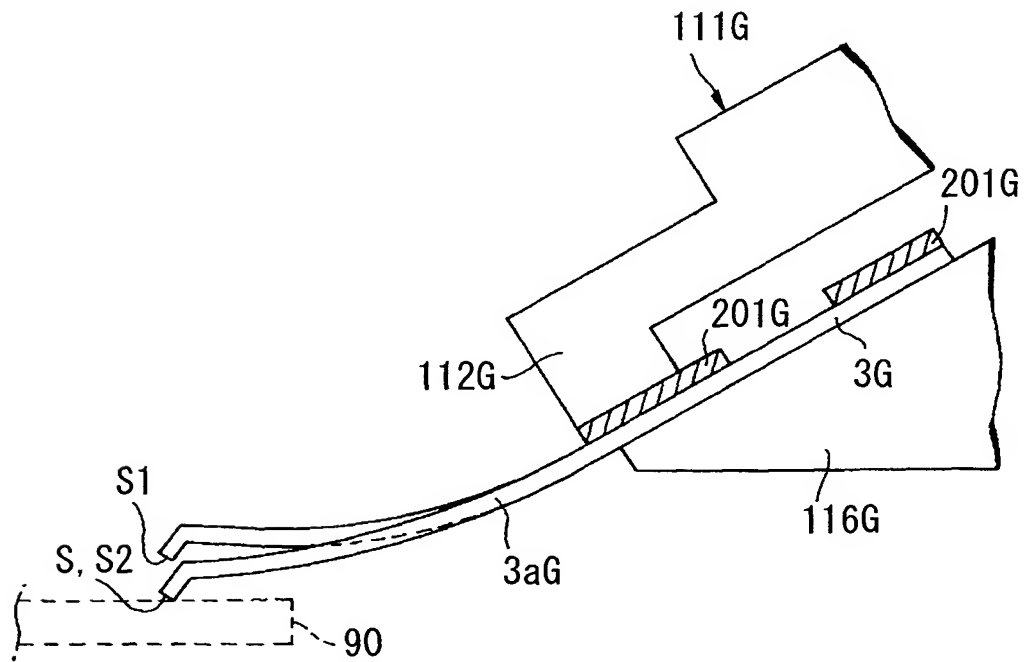
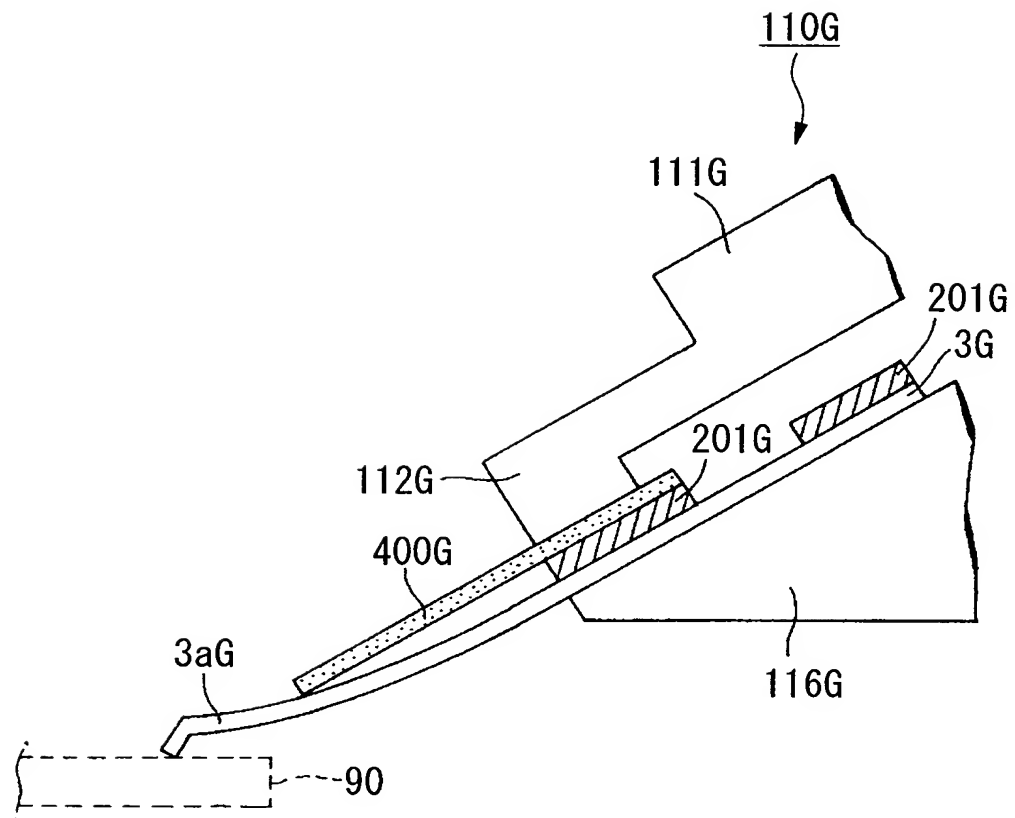




FIG. 43



10076508 061902

FIG. 44

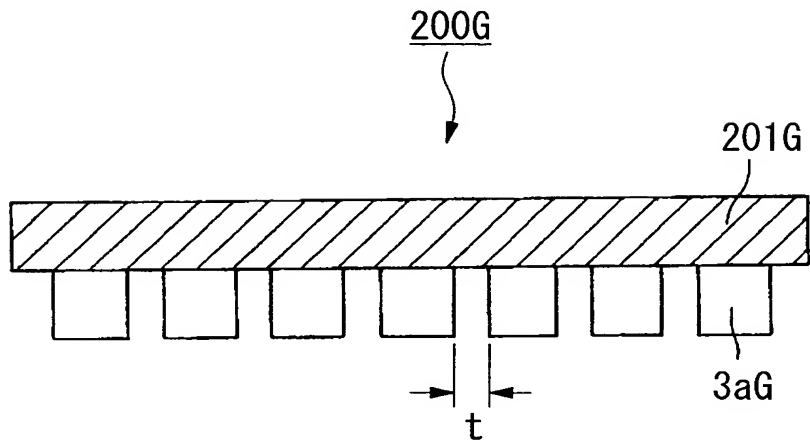


FIG. 45

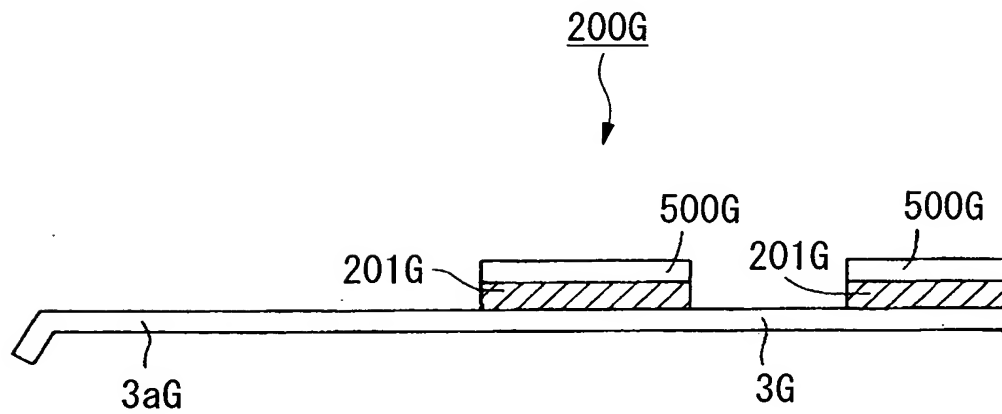


FIG. 46

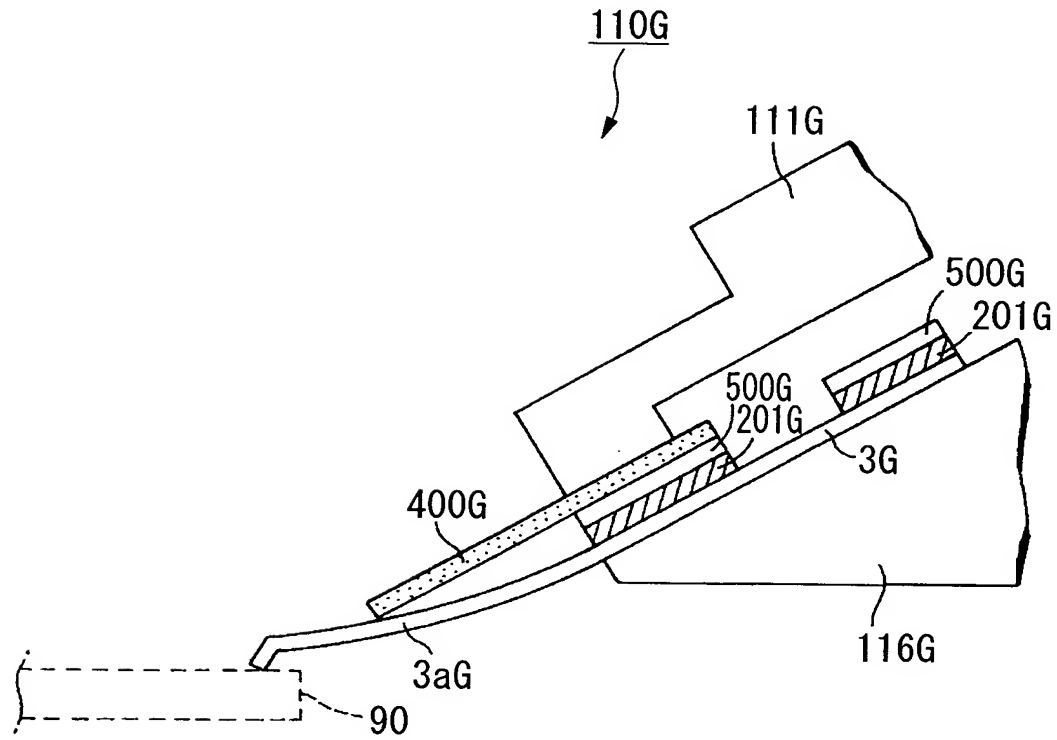


FIG. 47

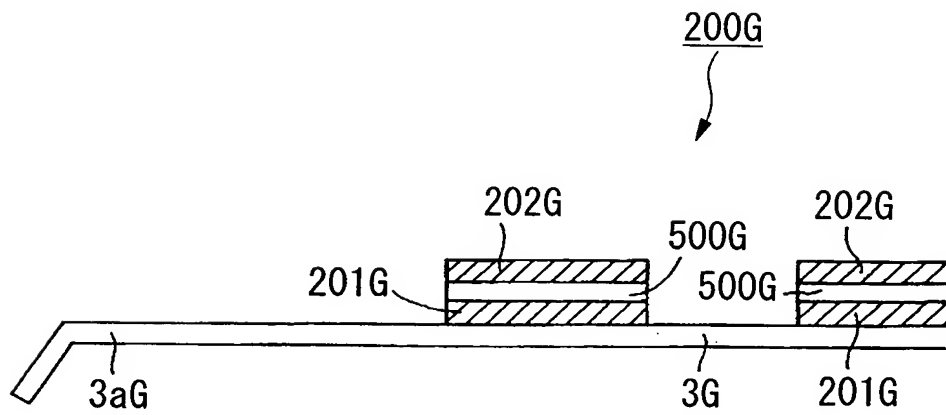


FIG. 48

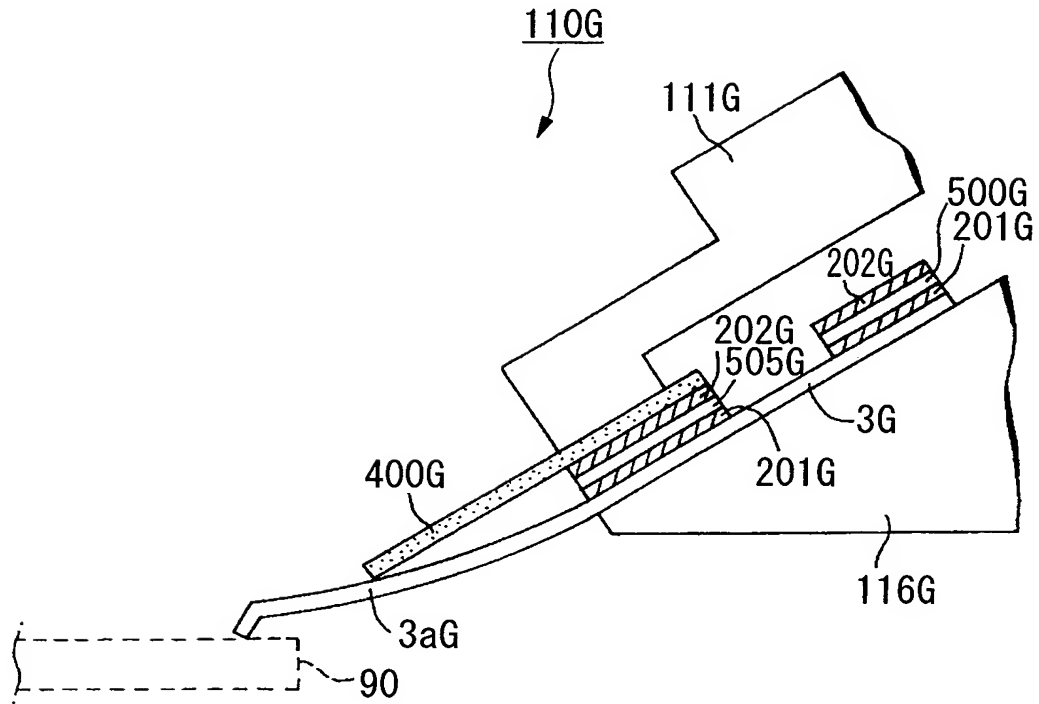


FIG. 49

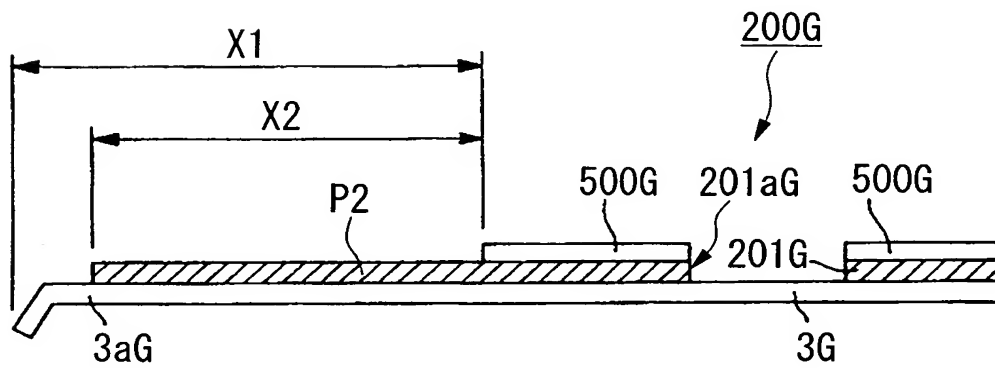


FIG. 50

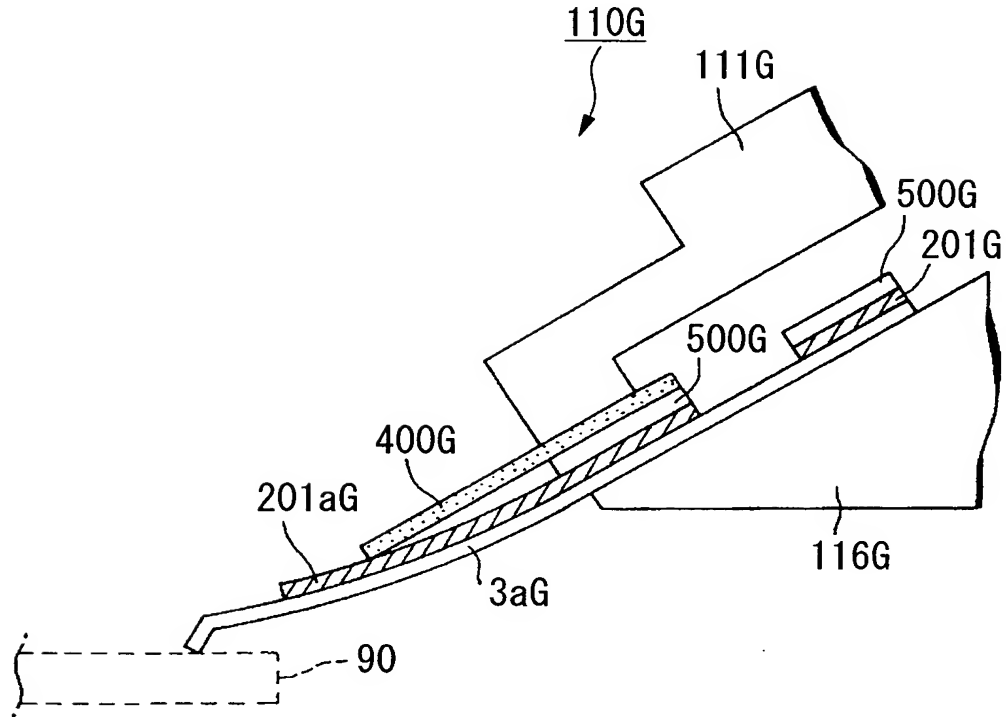
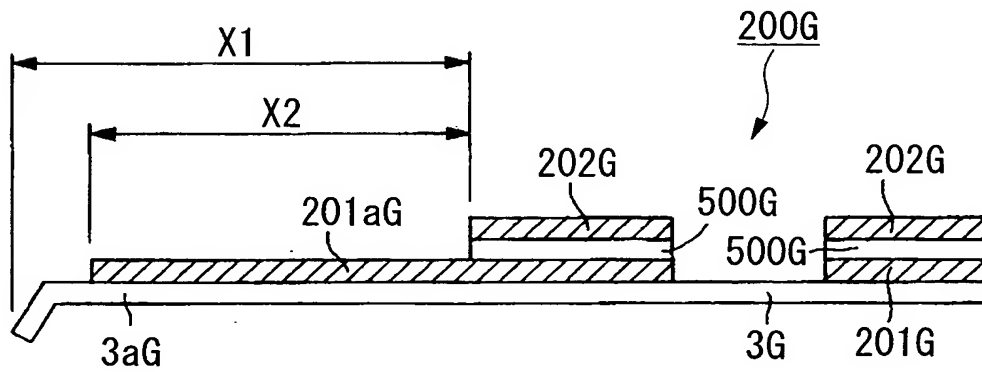
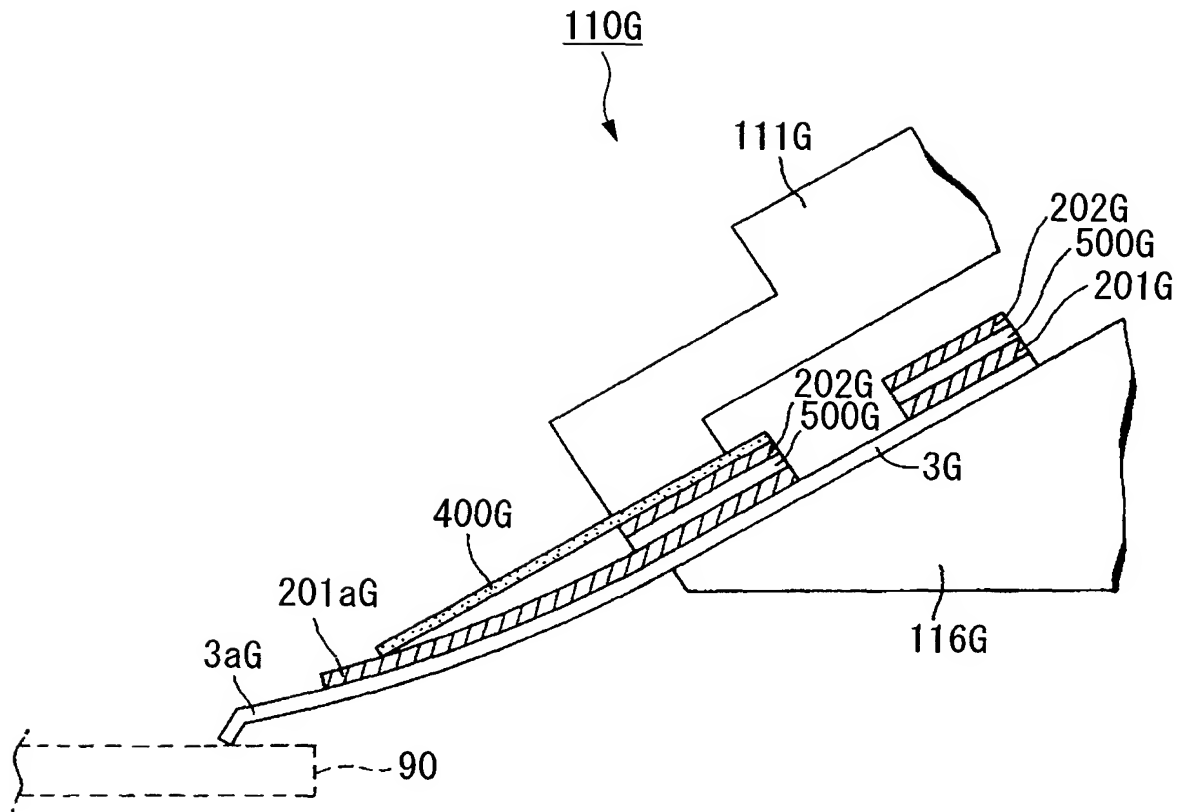


FIG. 51



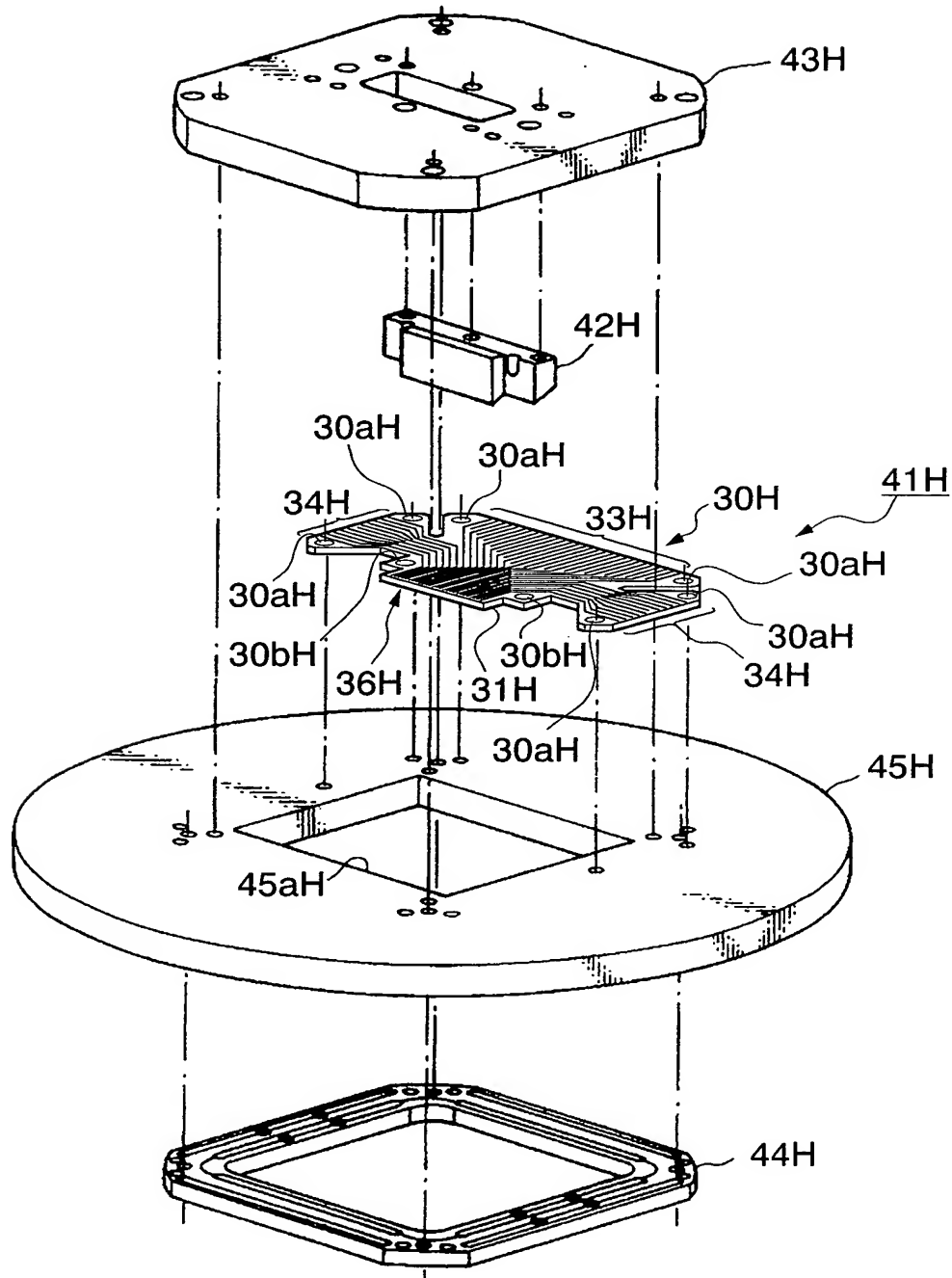
10076508-061901

FIG. 52



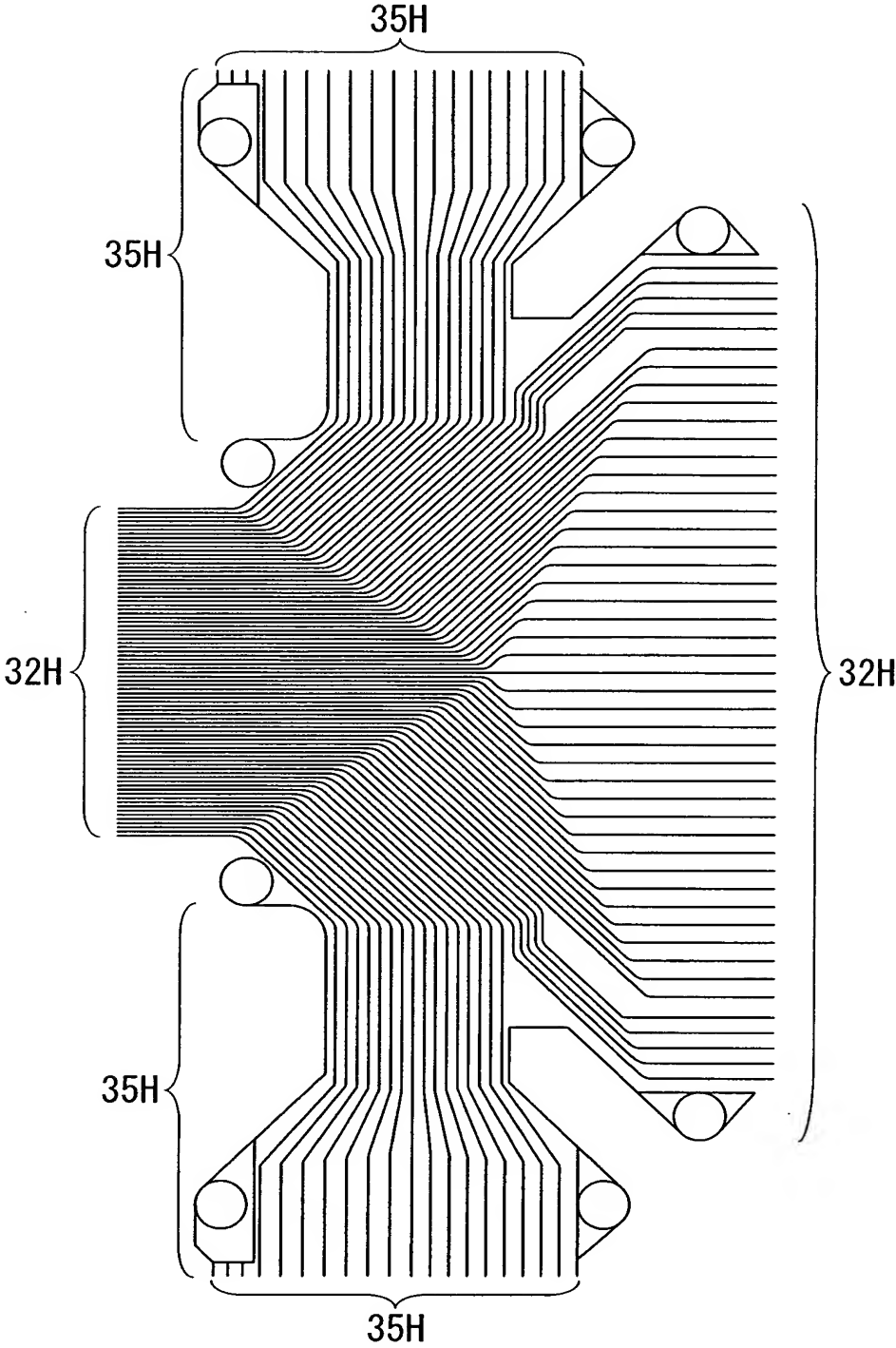
10076508-061902

FIG. 53



206190" 2059/001

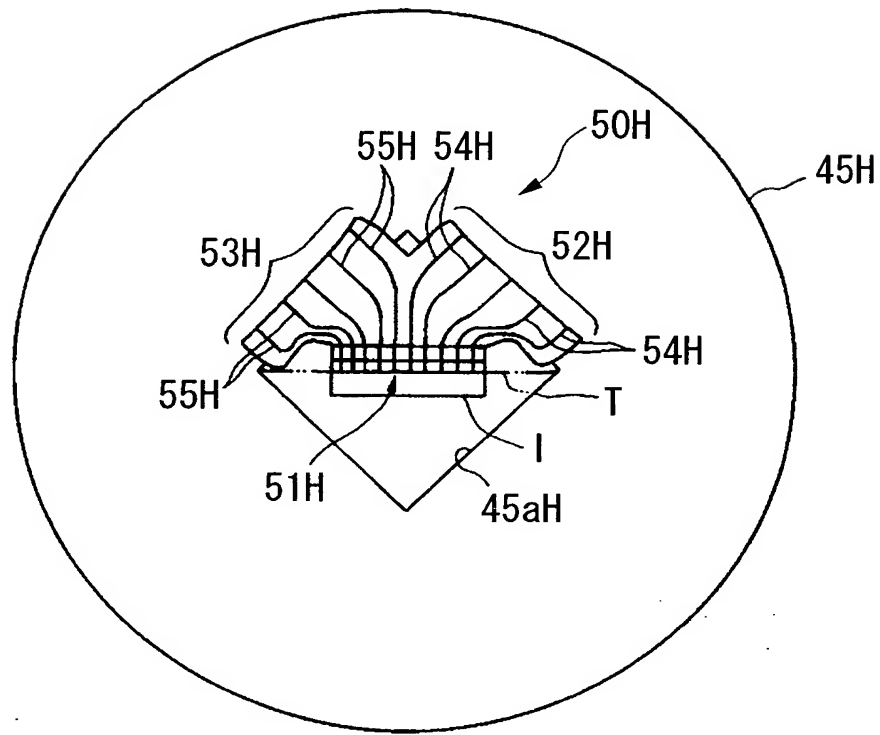
FIG. 54



2006190" 8059200T



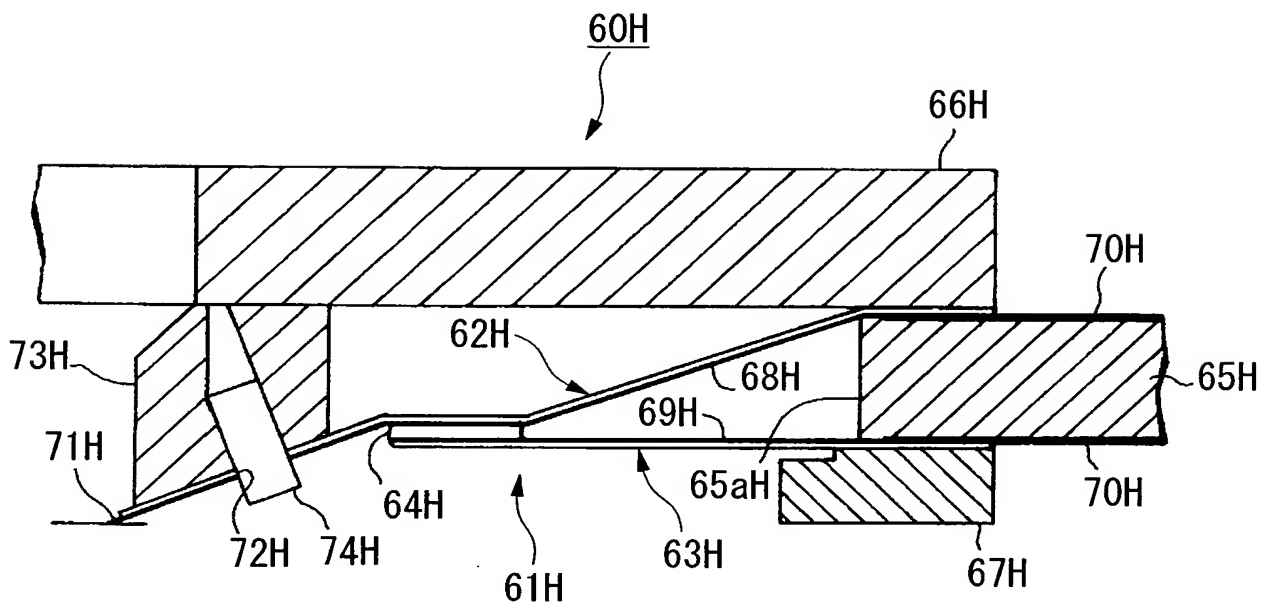
FIG. 55



2006T90" 8059Z00F



FIG. 57



10076508.061902

FIG. 58

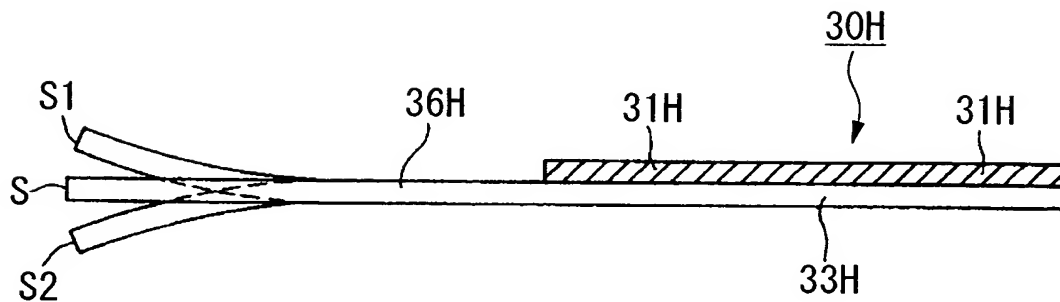
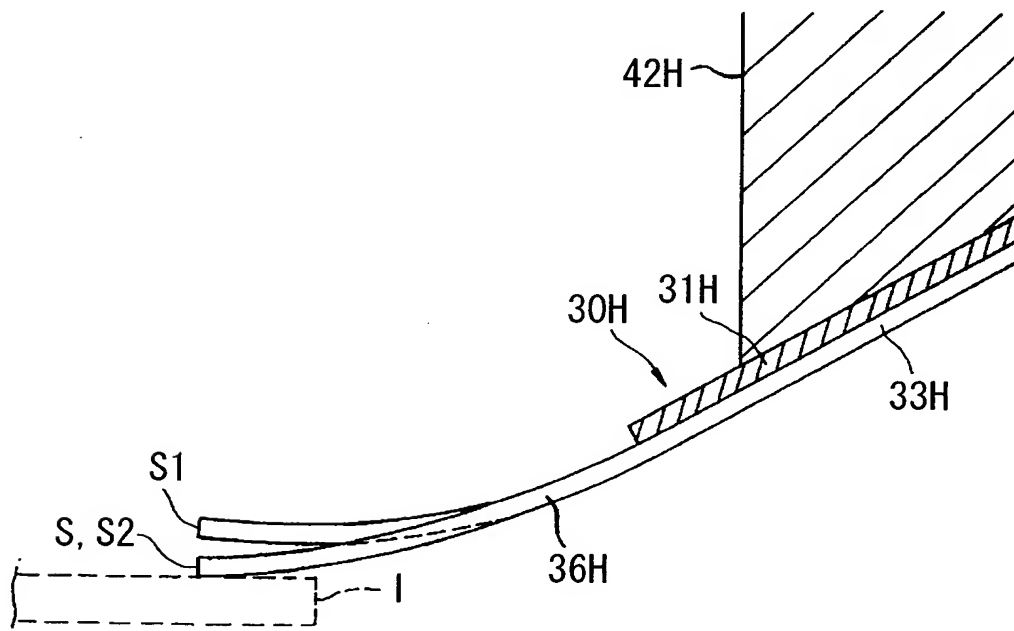


FIG. 59



10076508-061902

FIG. 60

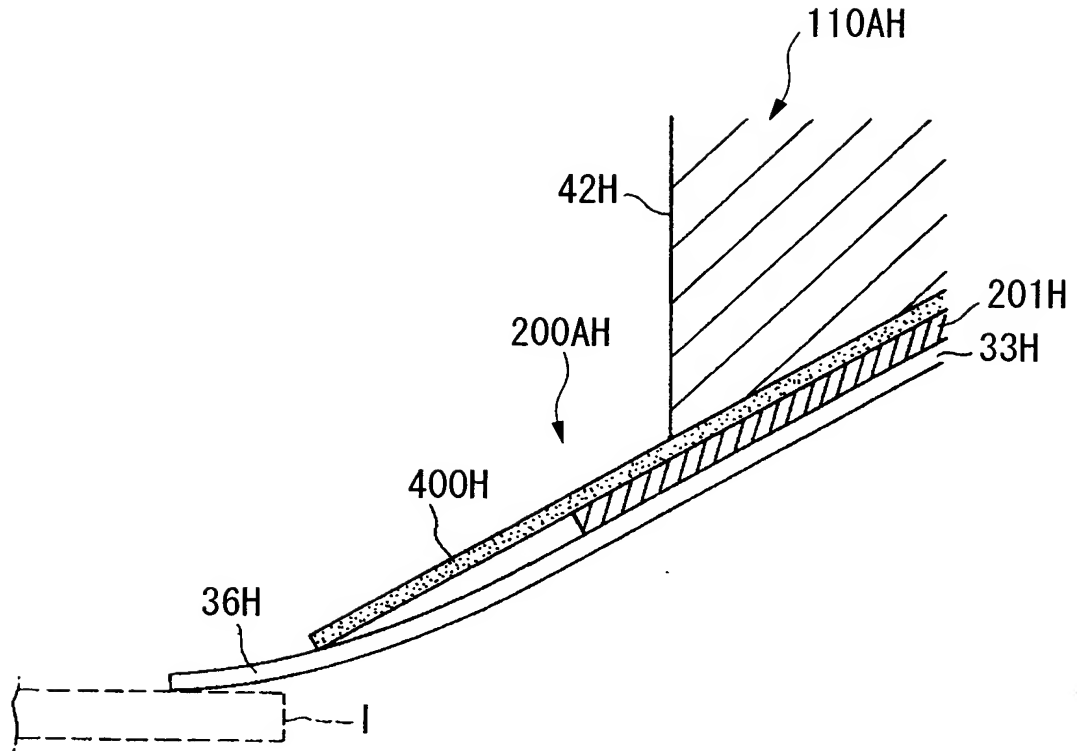
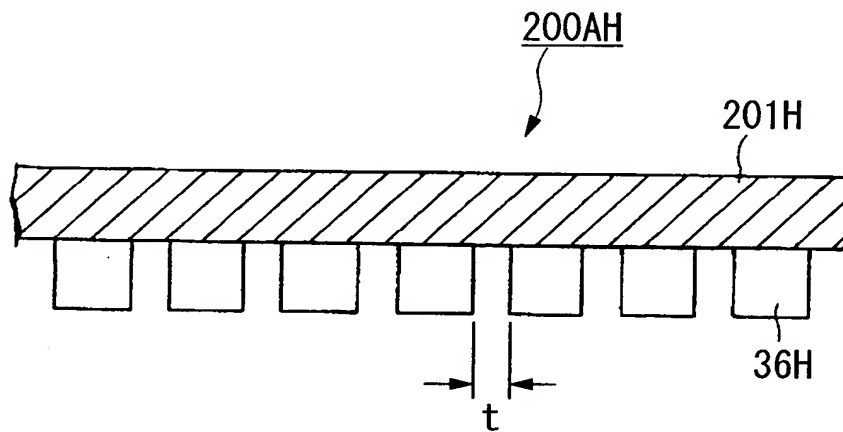


FIG. 61



206T90" 80594.00T

FIG. 62

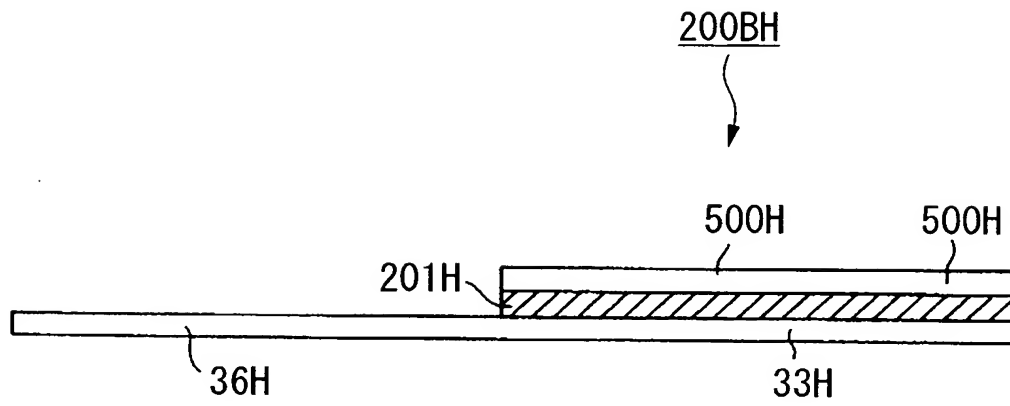
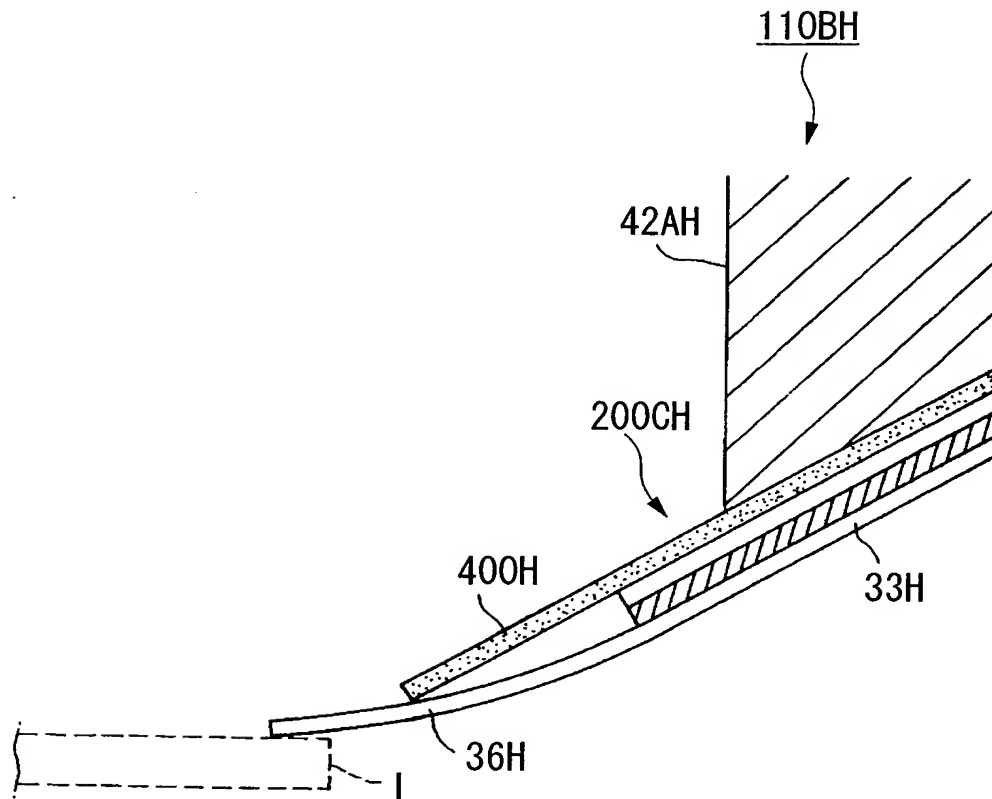


FIG. 63



206T90" 8059/00T

FIG. 64

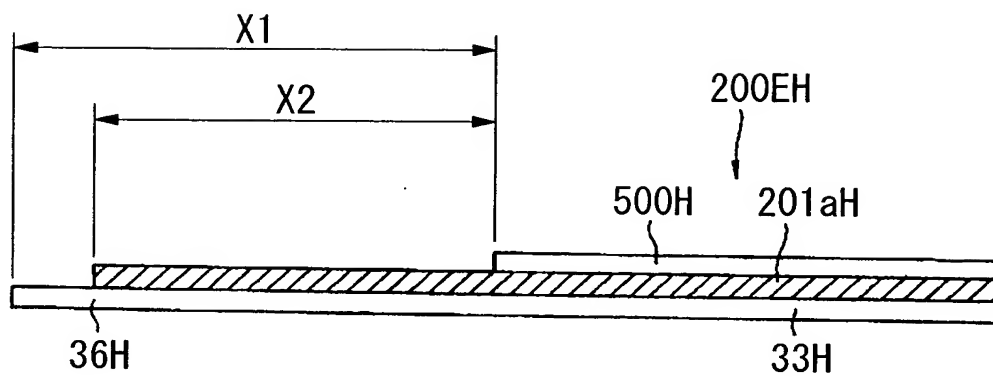
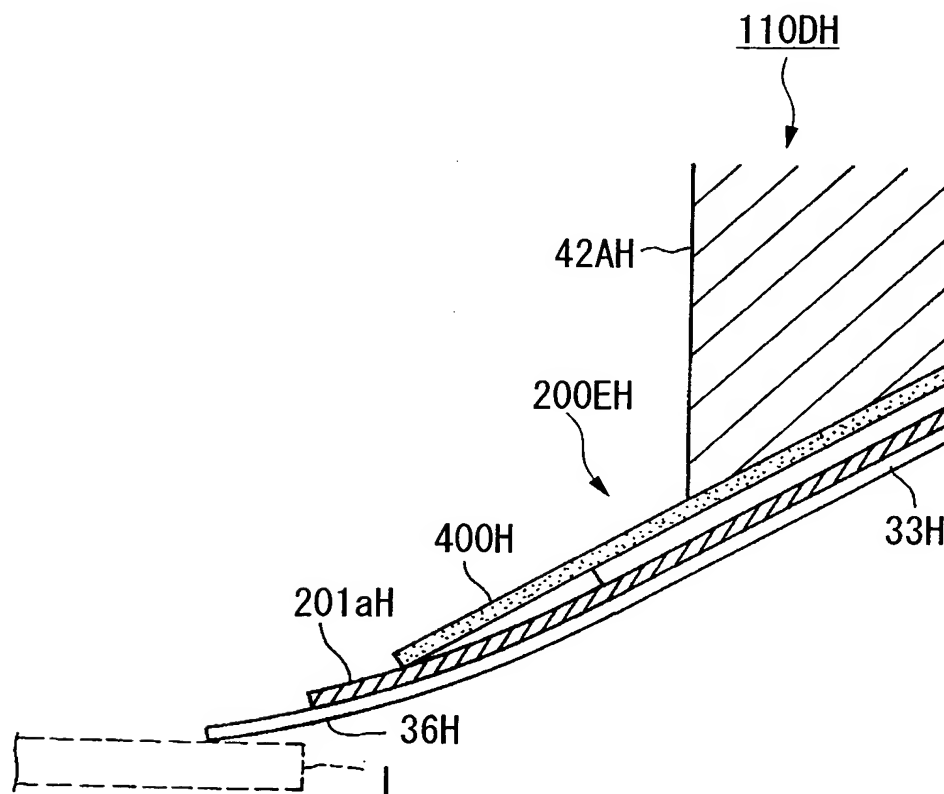
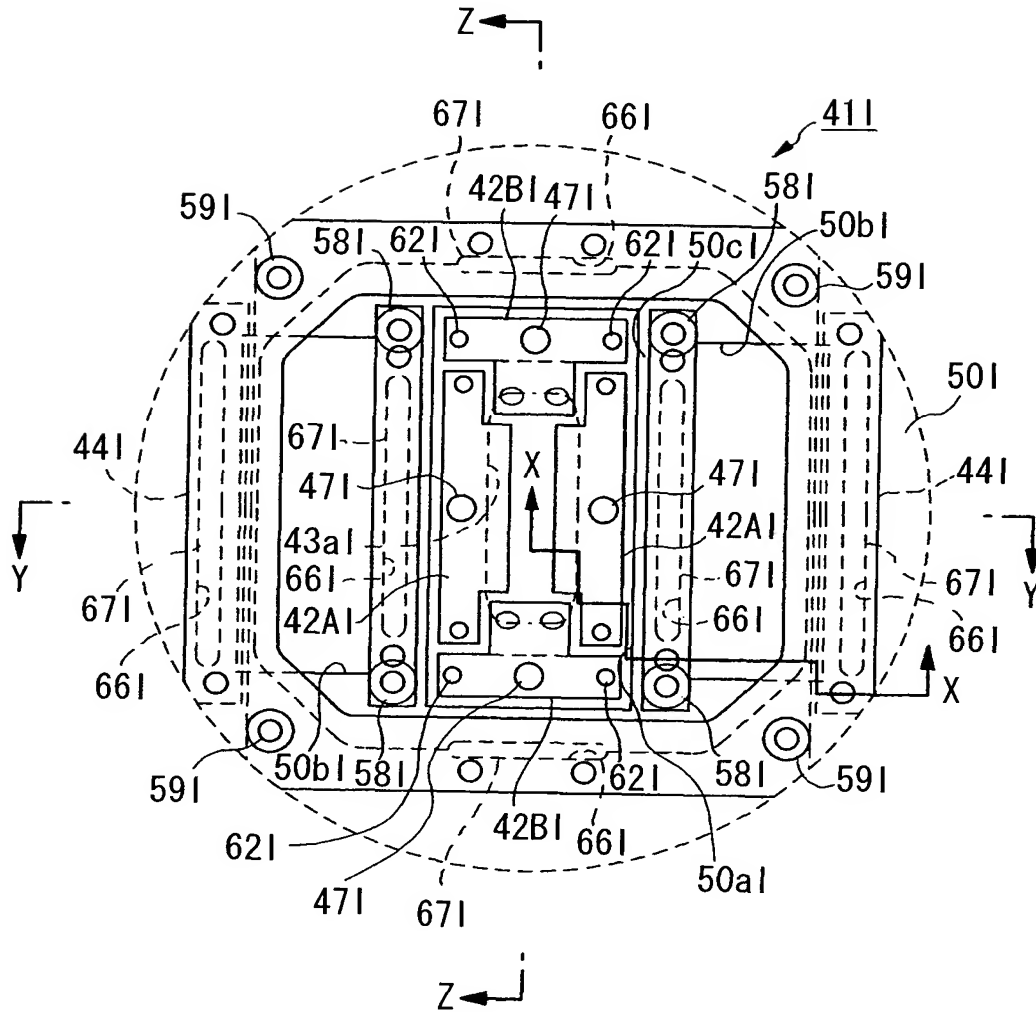


FIG. 65



10076508-001902

FIG. 66

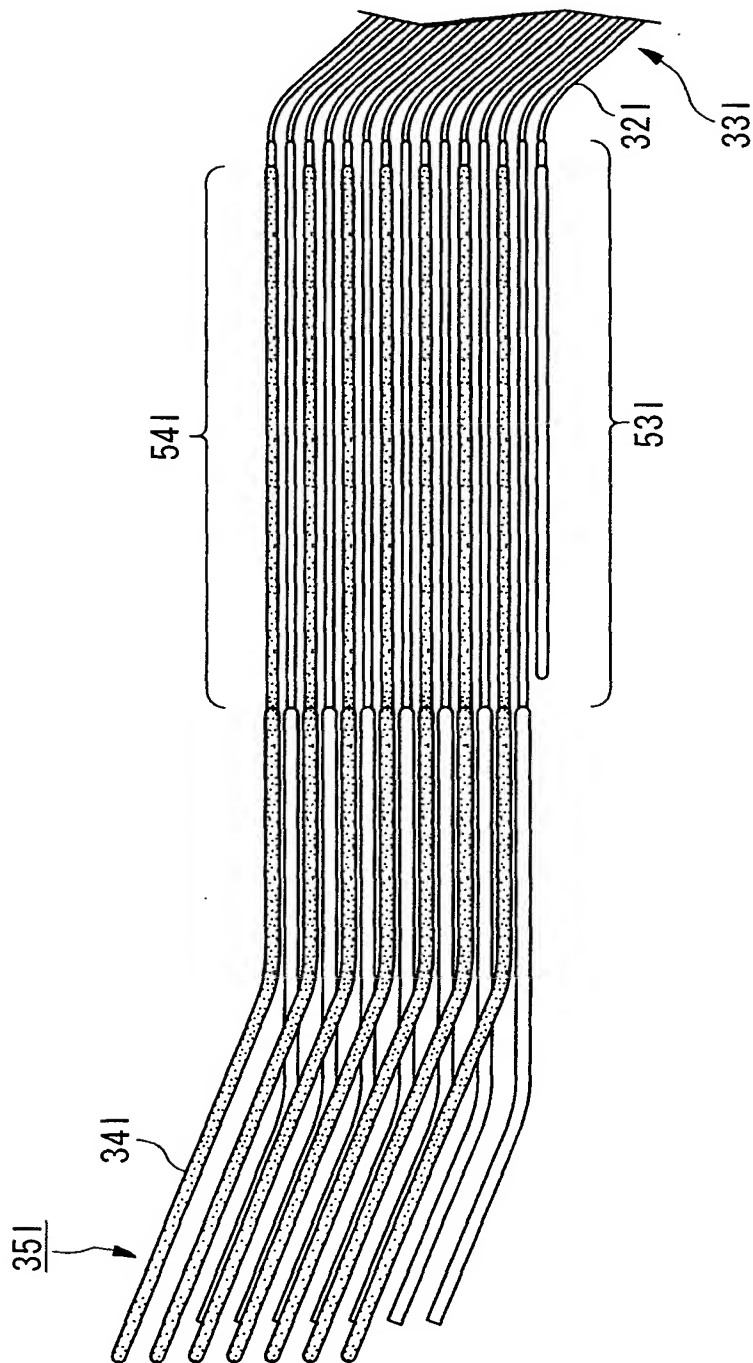


10076508-061902



[illegible]

FIG. 68



This cross-sectional diagram illustrates a multi-layered semiconductor structure. It features a central core layer (43) flanked by side regions (42A and 43a). The top surface is covered by a thin layer (67), which is patterned into various shapes, including rectangular blocks (44) and trapezoidal structures (41). Below the core, there are several other layers and components, including a base layer (50), a middle layer (66), and a bottom layer (45). Various electrical contacts and interconnects are shown, labeled with numbers such as 30, 31, 33, 35, 36, 41, 42, 43, 44, 45, 46, 50, 66, and 67. Arrows indicate specific features or connections within the device.



FIG. 71

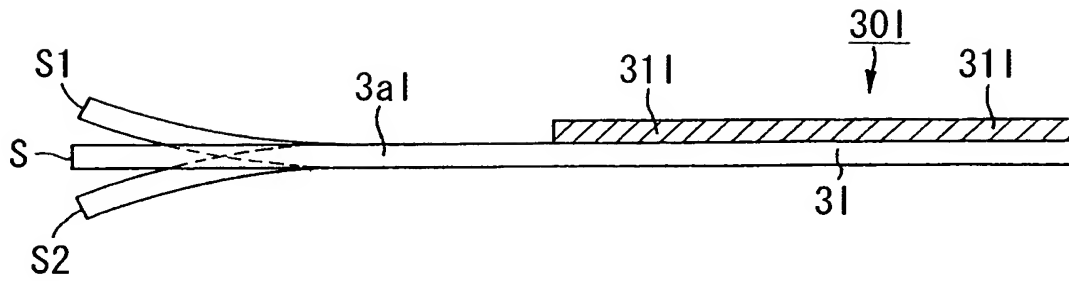
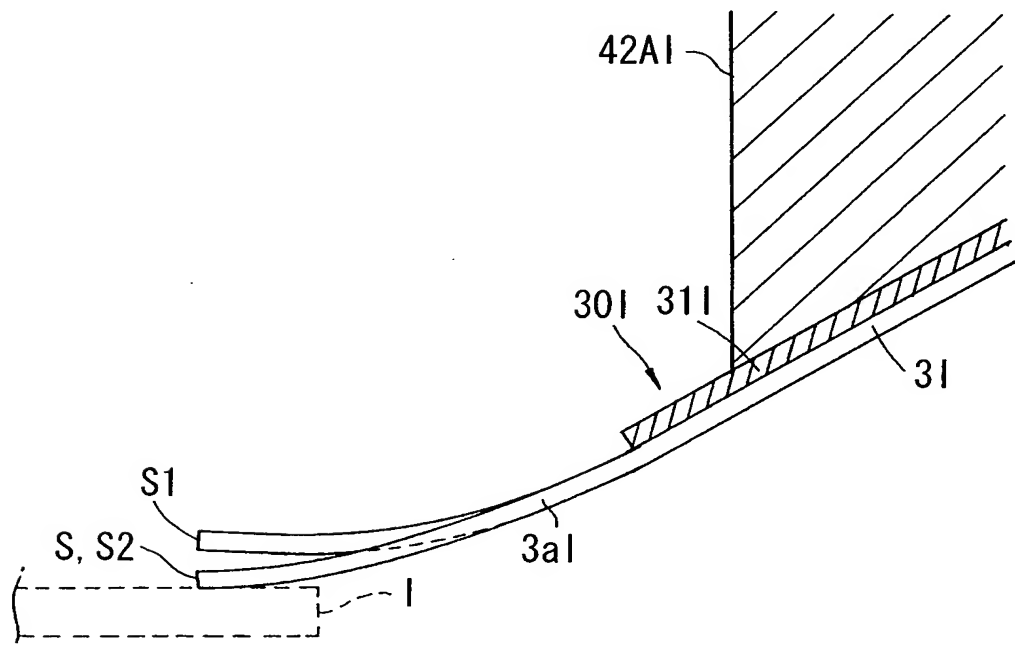


FIG. 72



206T90" 8059/00T

FIG. 73

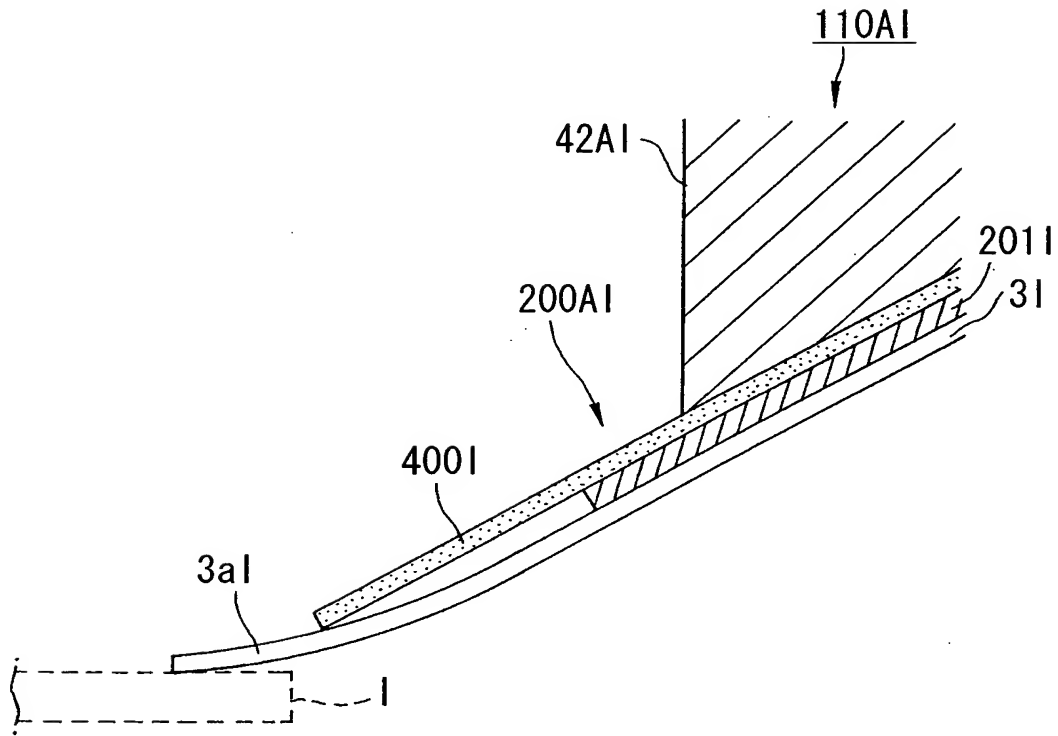


FIG. 74

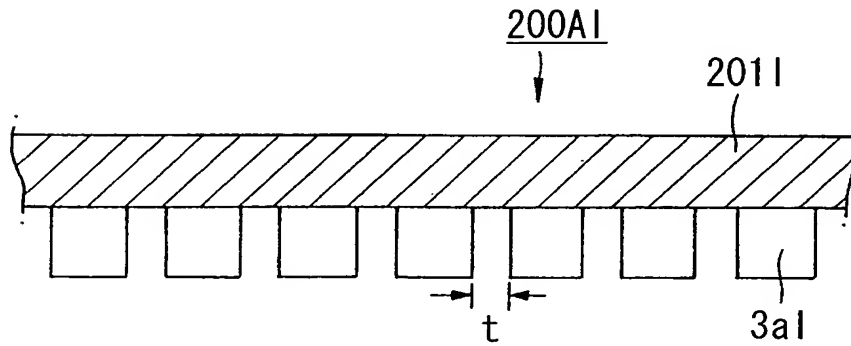


FIG. 75

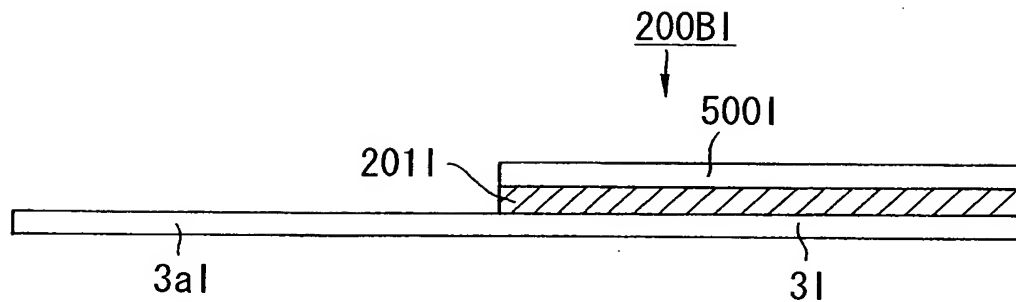


FIG. 76

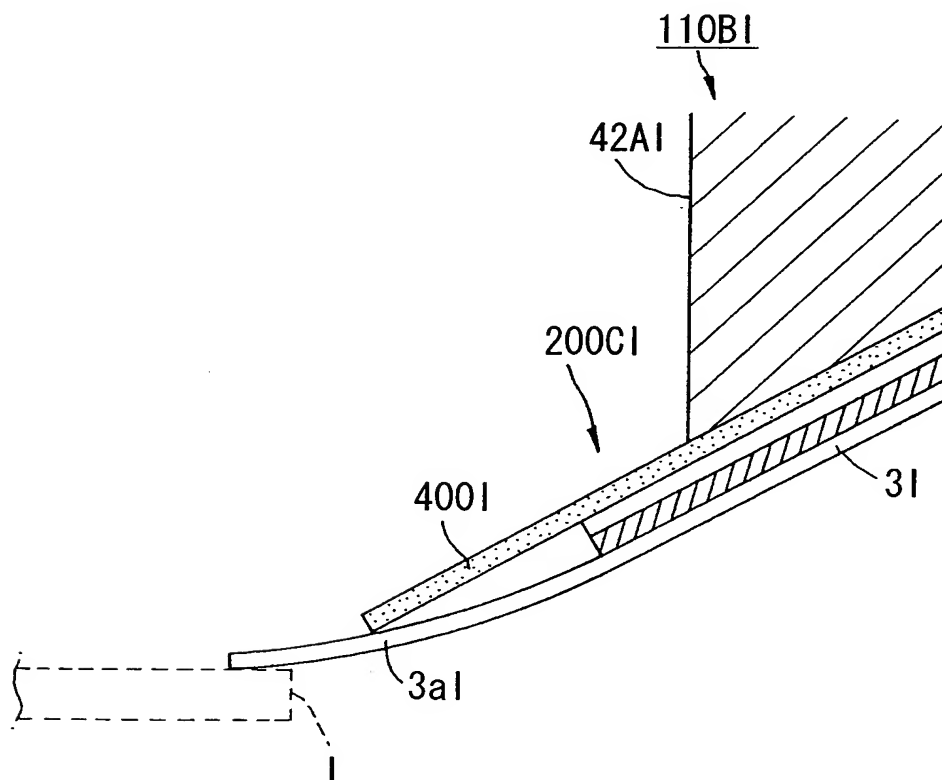


FIG. 77

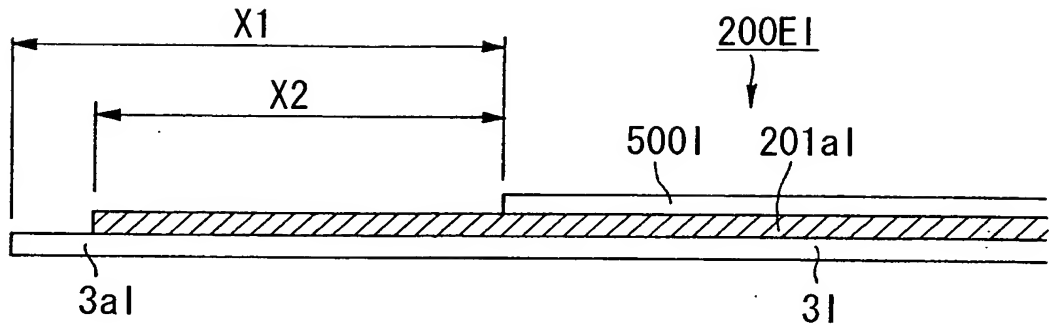
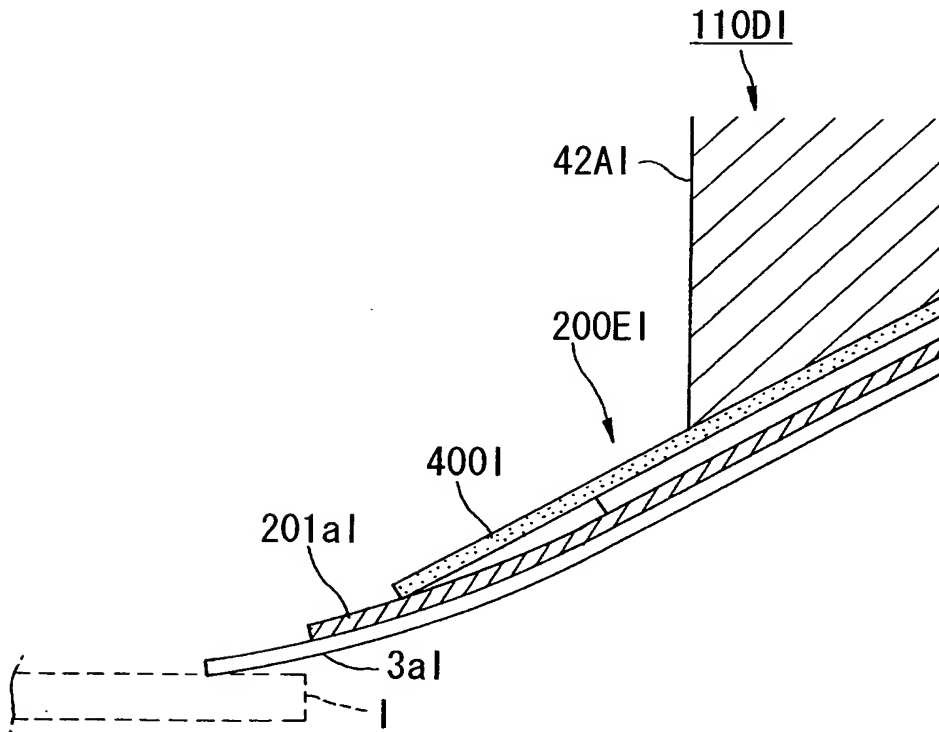


FIG. 78



206T90" 8059/00T



FIG. 79

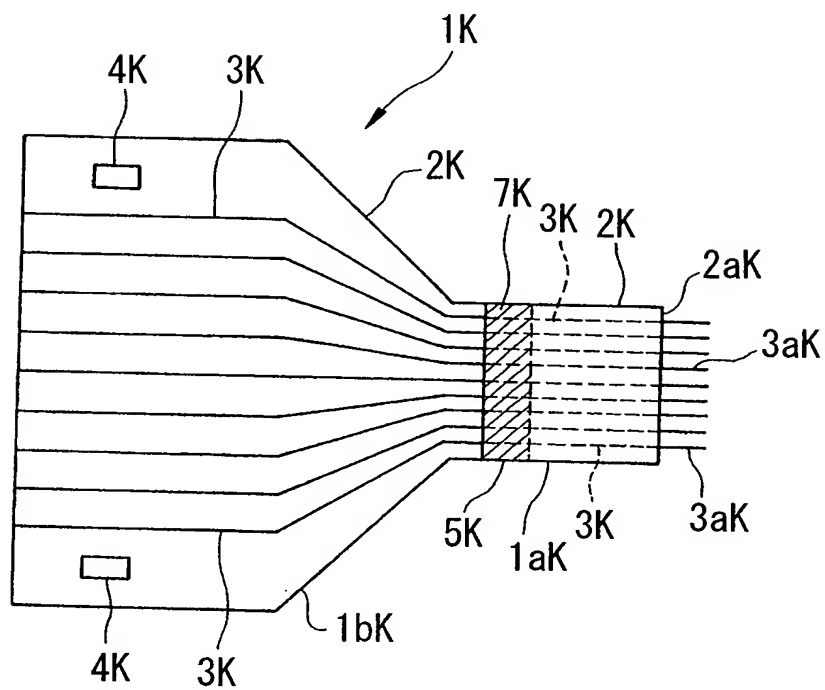


FIG. 80

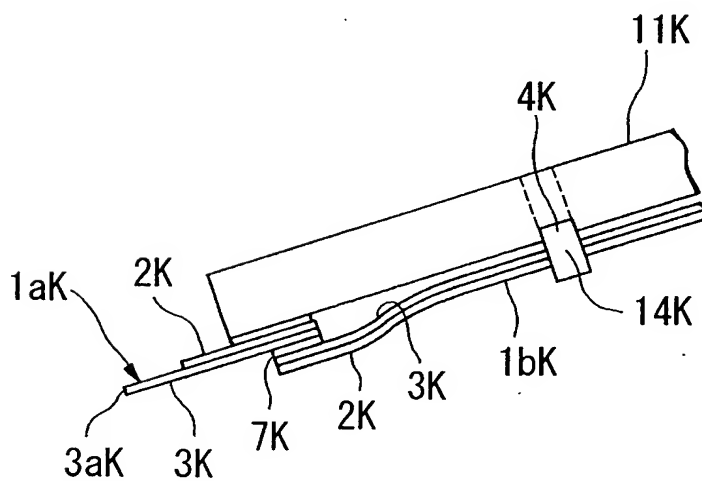


FIG. 81

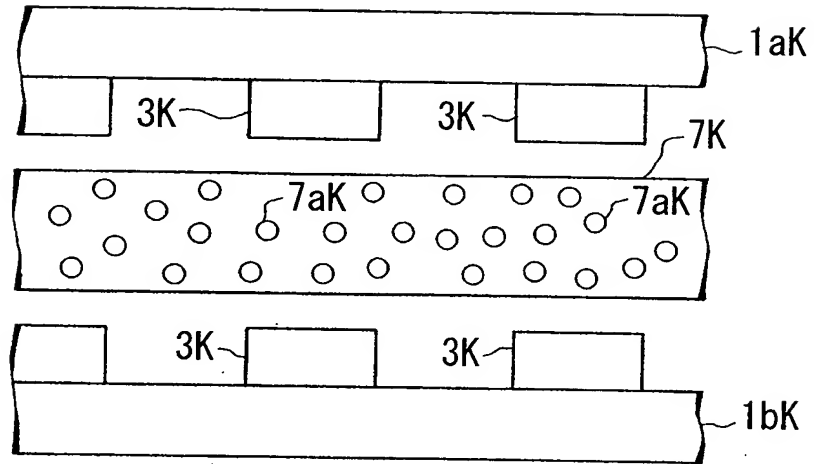
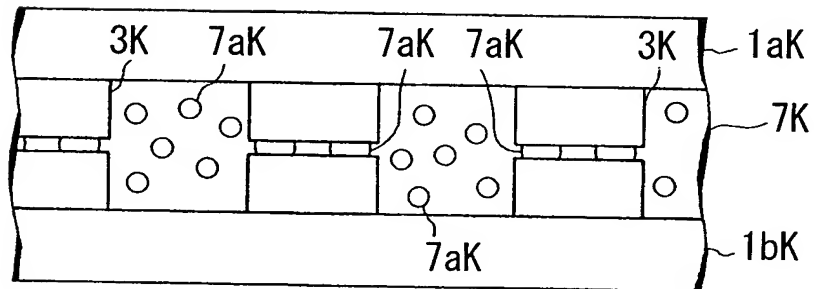


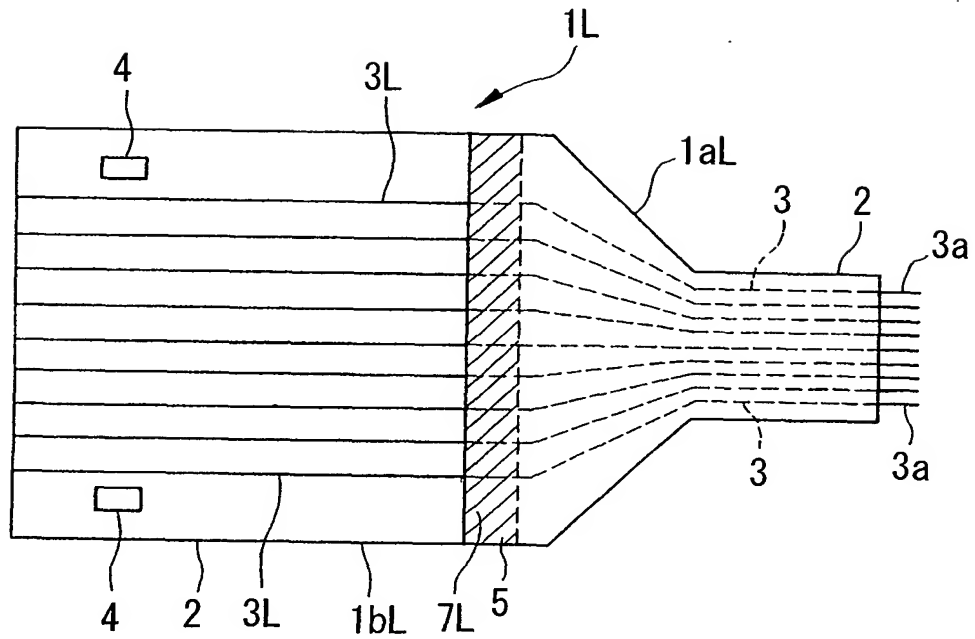
FIG. 82



10076508-061902

[illegible]

FIG. 84



10076508-05190T

FIG. 85

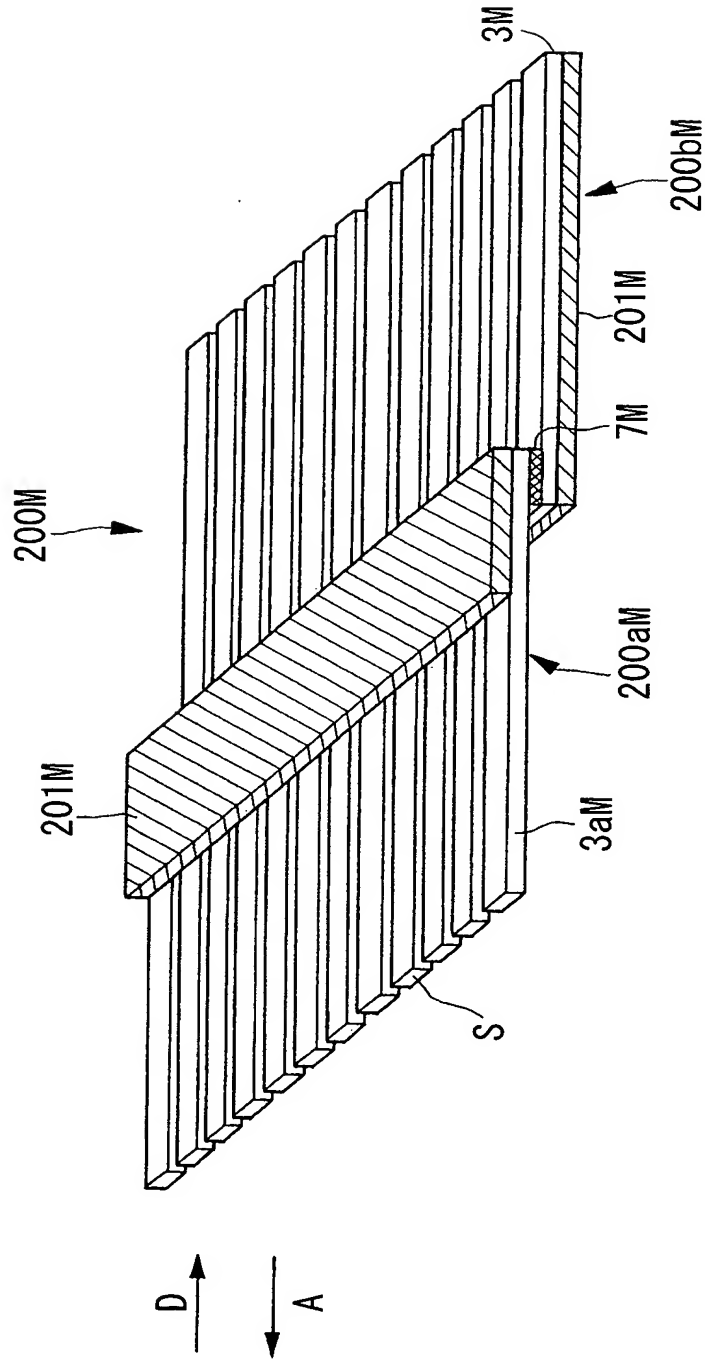
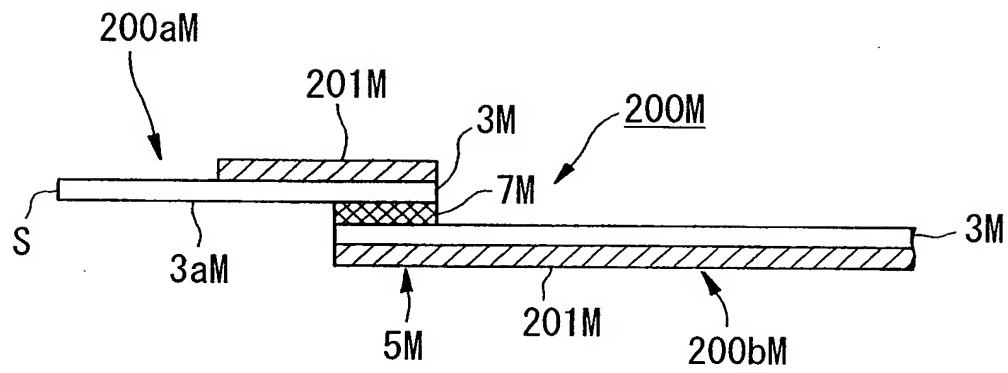


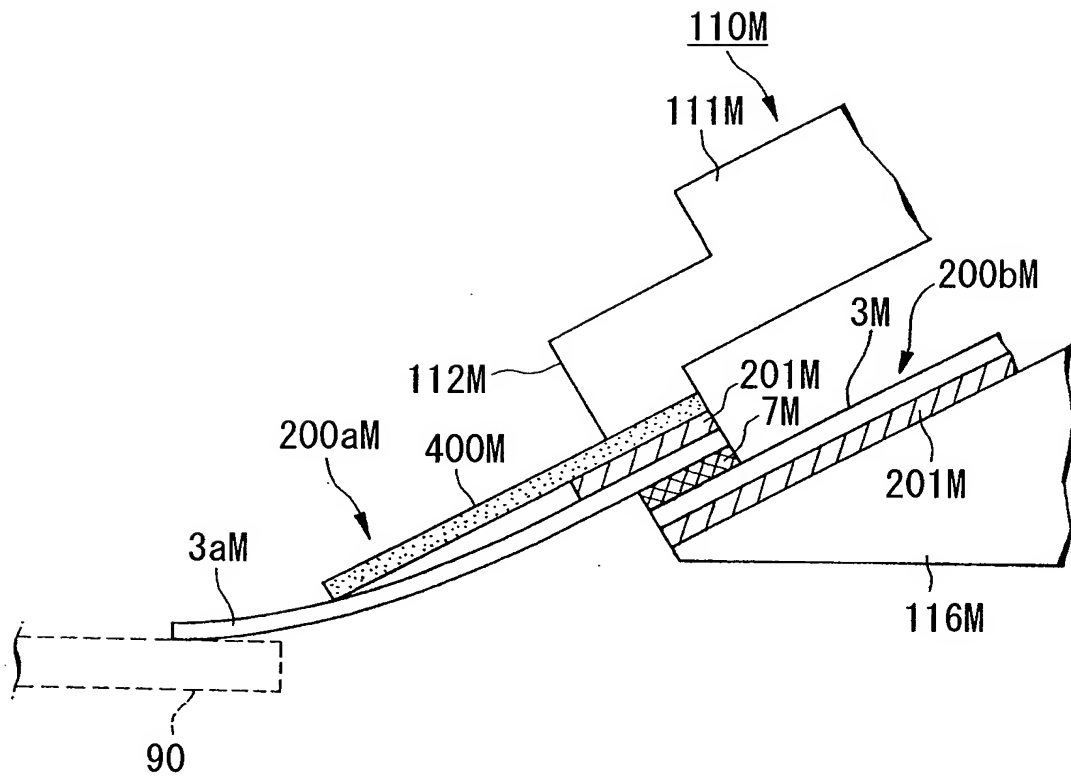
FIG. 86



10076508.061902



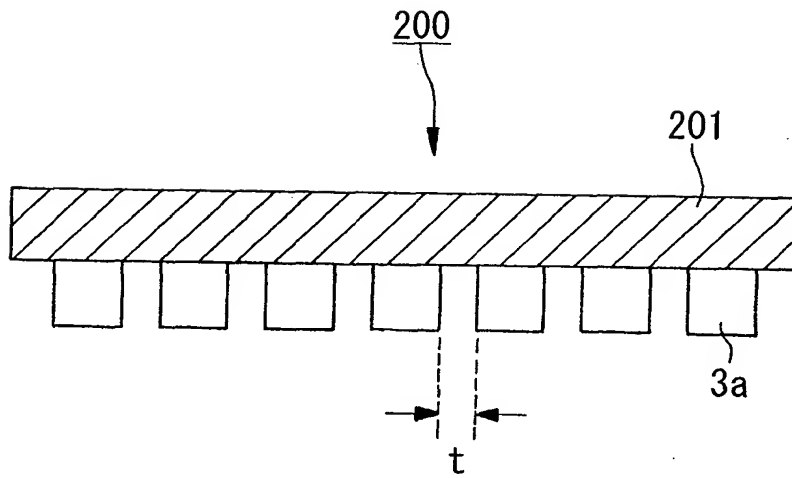
FIG. 89



10076508-061902

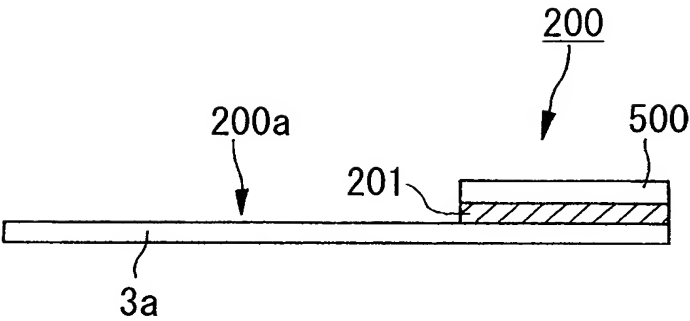


FIG. 90



10076508-061902

FIG. 91



206T90-8059/001

FIG. 92

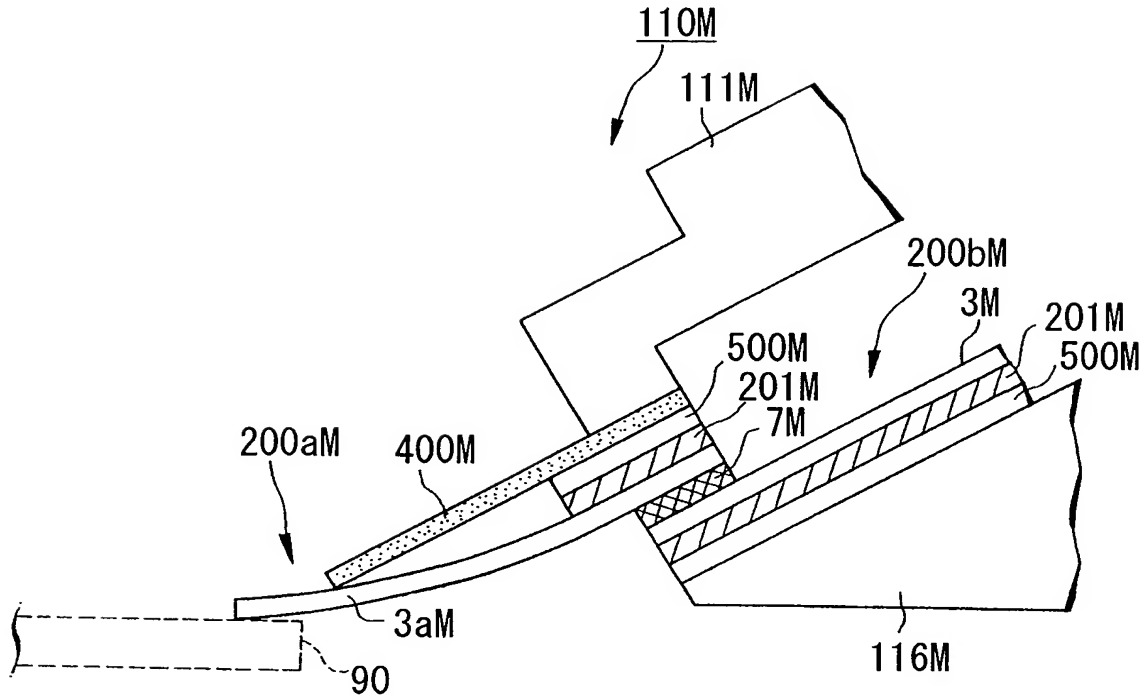
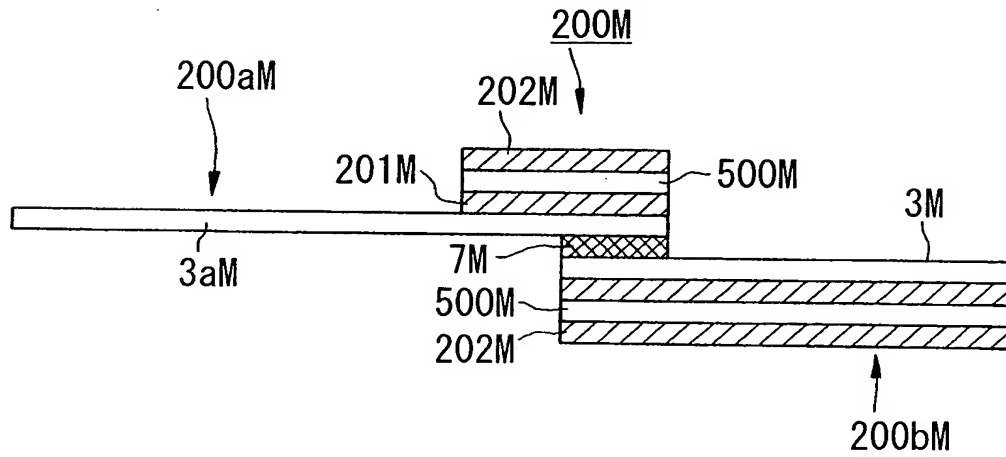


FIG. 93



10076508-061900

Diagram illustrating a cross-sectional view of a semiconductor device 200M. The device includes a substrate 3aM, a first layer 201M, and a second layer 201aM. Dimensions X1 and X2 are indicated. A cross-hatched layer 7M is shown between the first and second layers. A third layer 3M is shown on the right side of the device.

FIG. 96

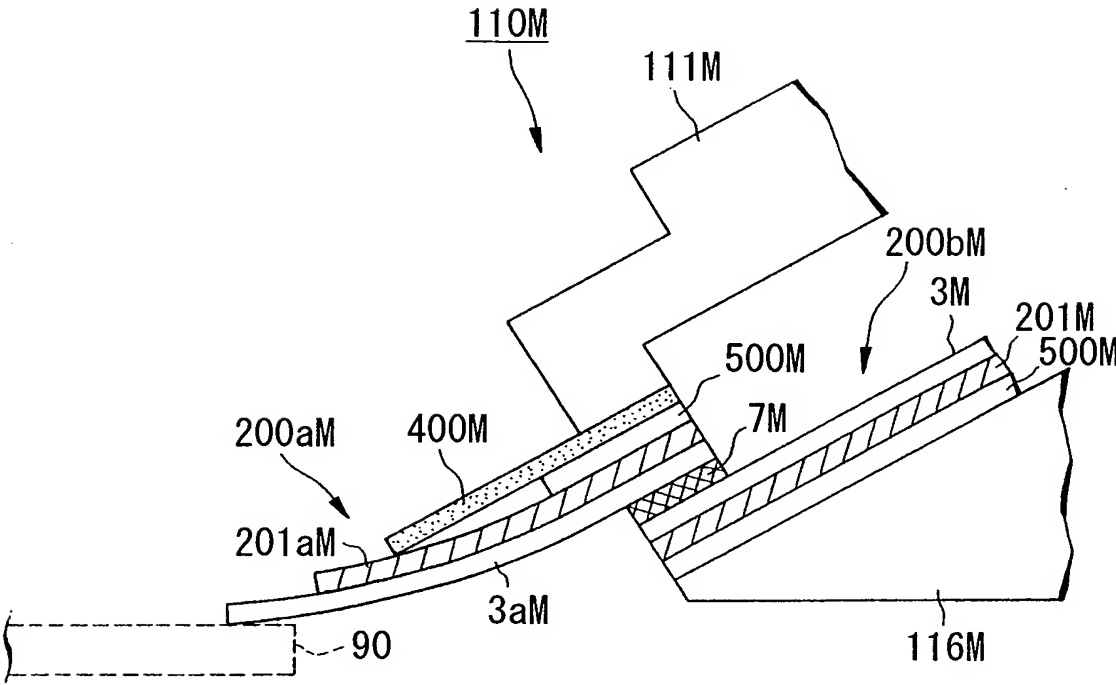


FIG. 97

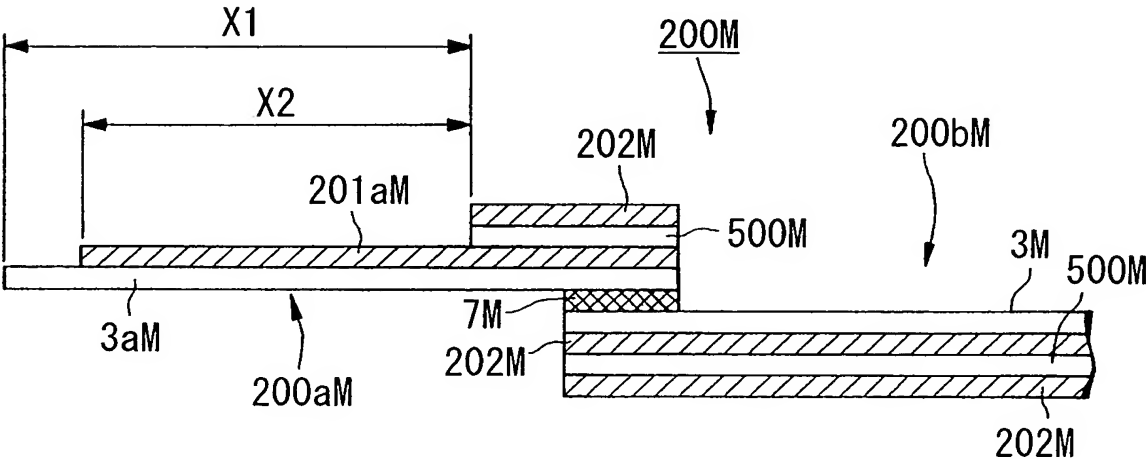
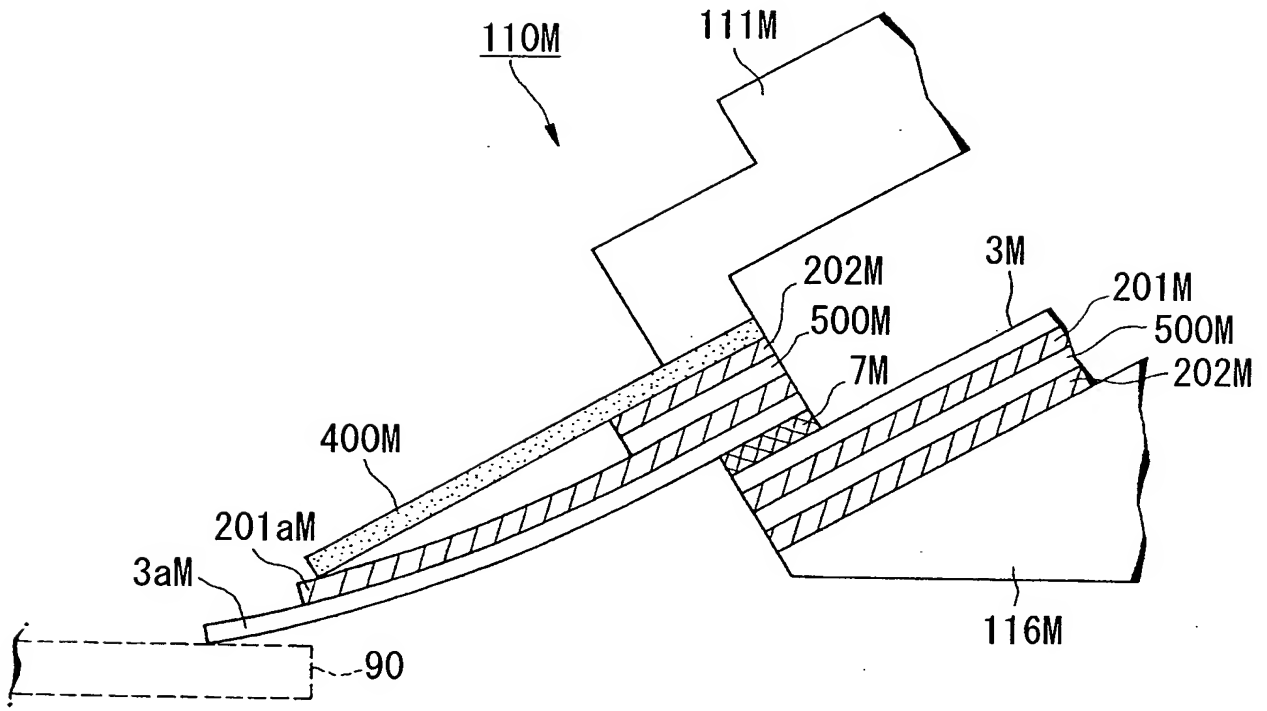
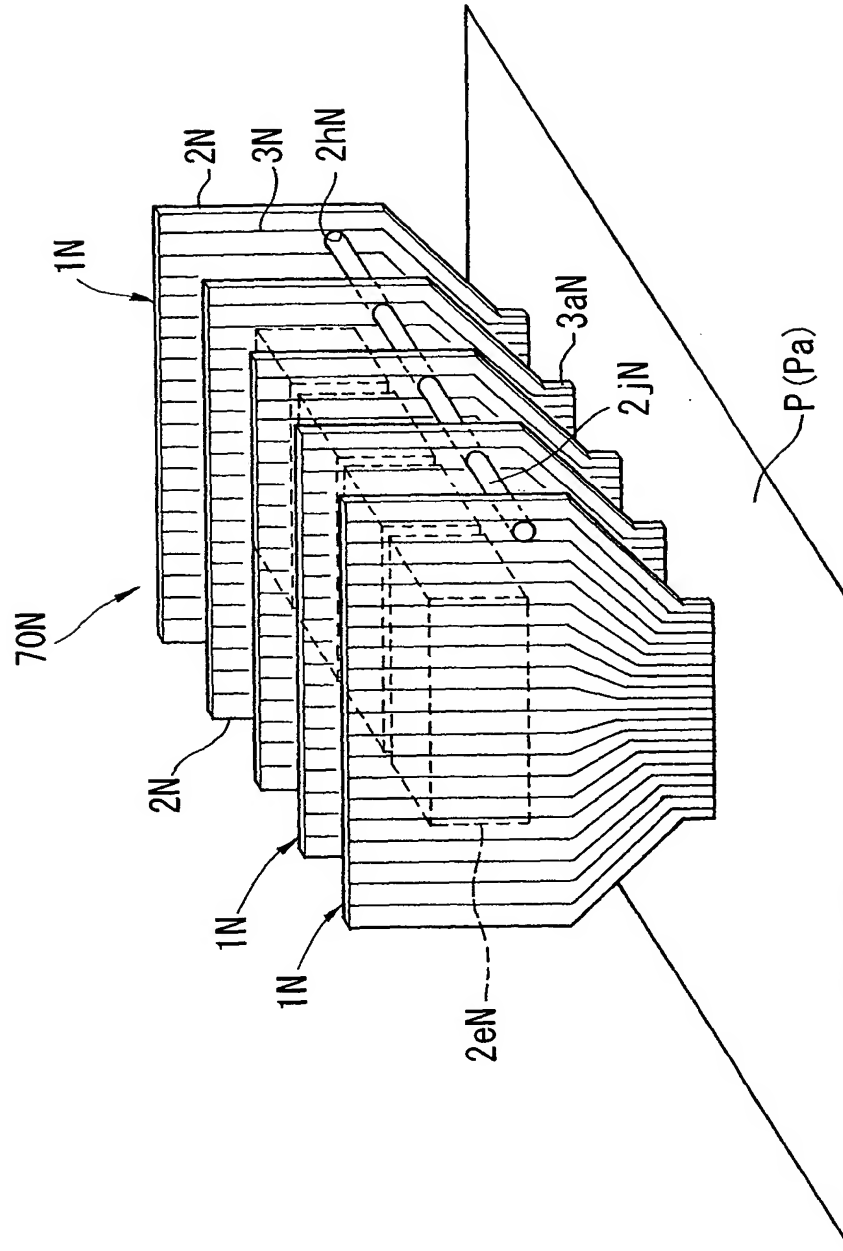


FIG. 98



10076508.061902

FIG. 99



206T50" 8059/00T

FIG. 100

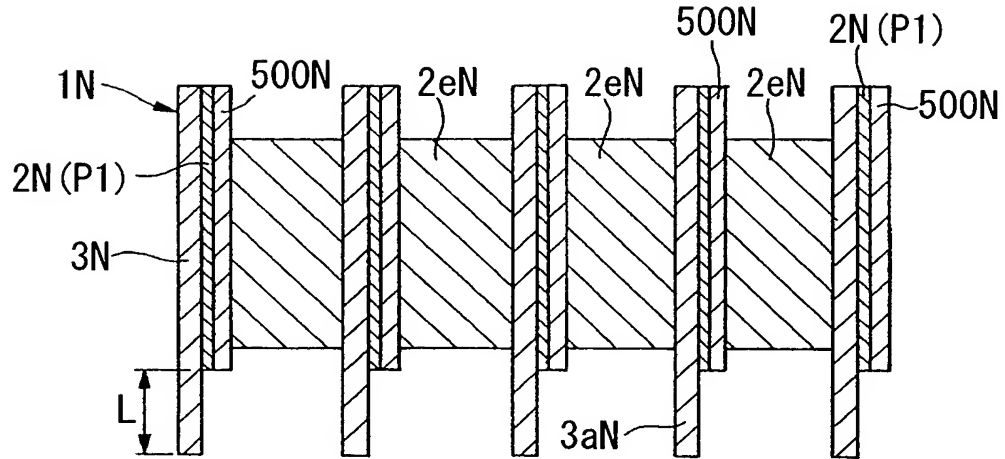
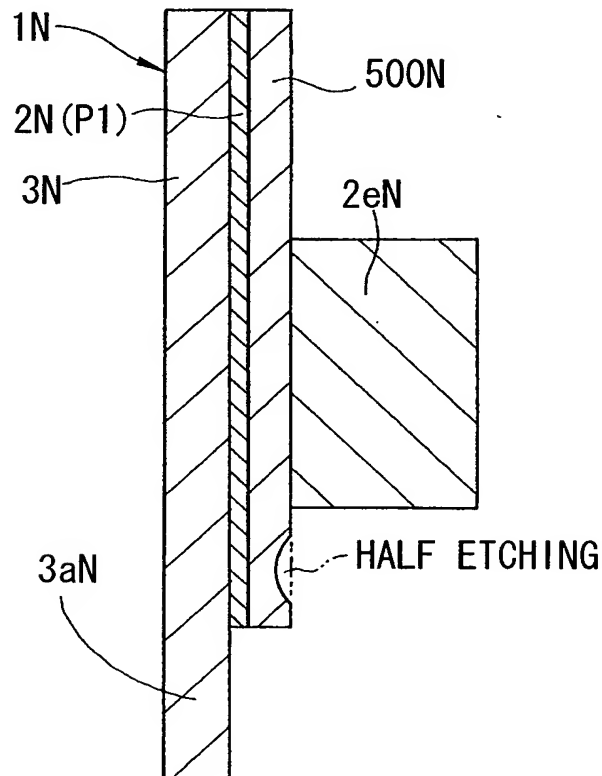


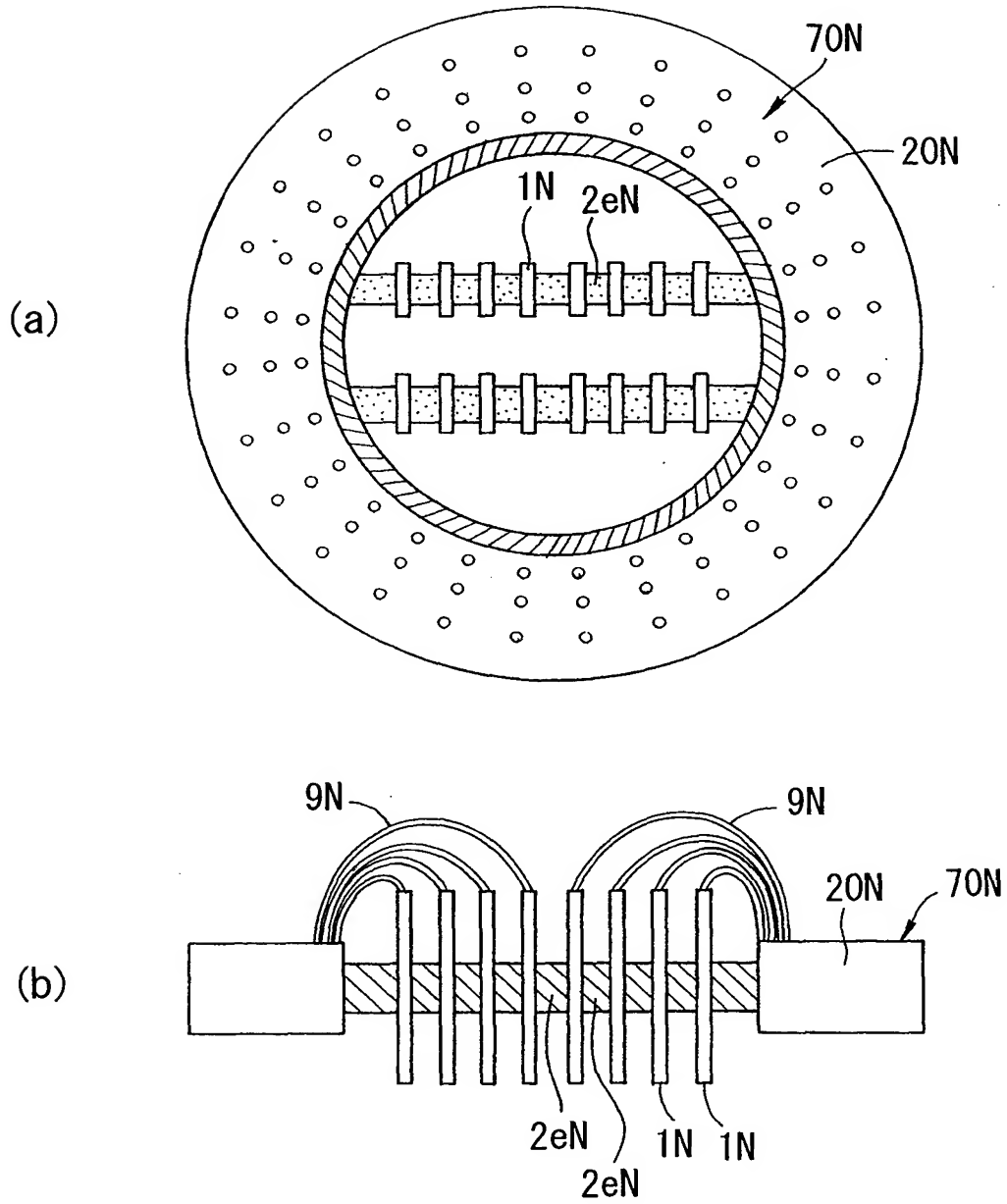
FIG. 101



1006508-001902

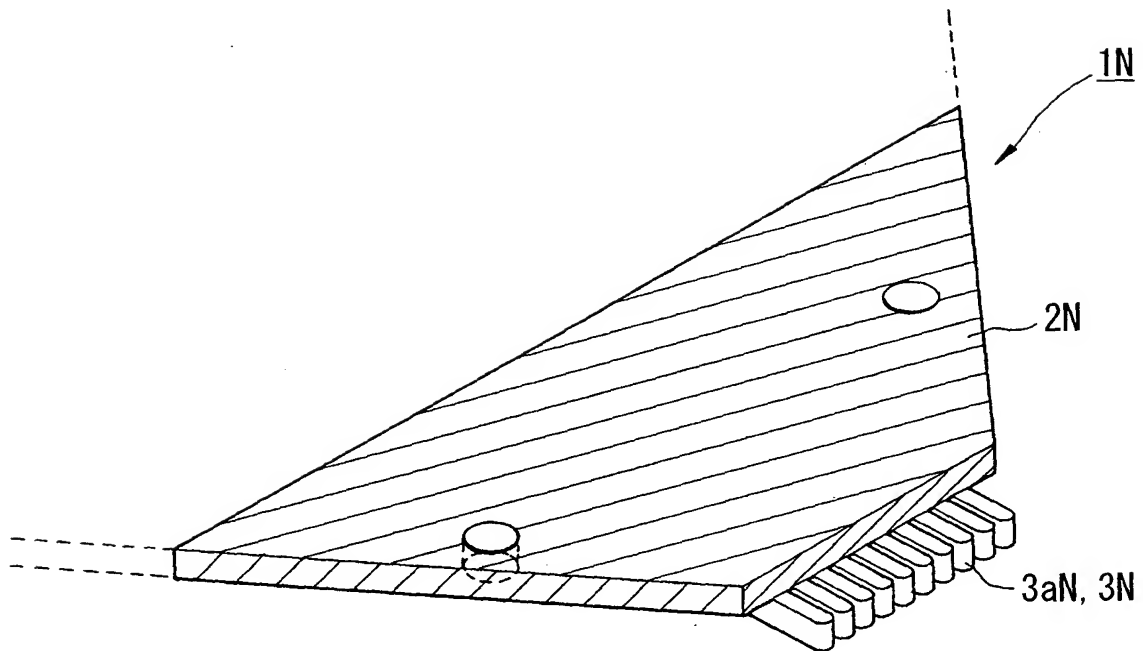


FIG. 102



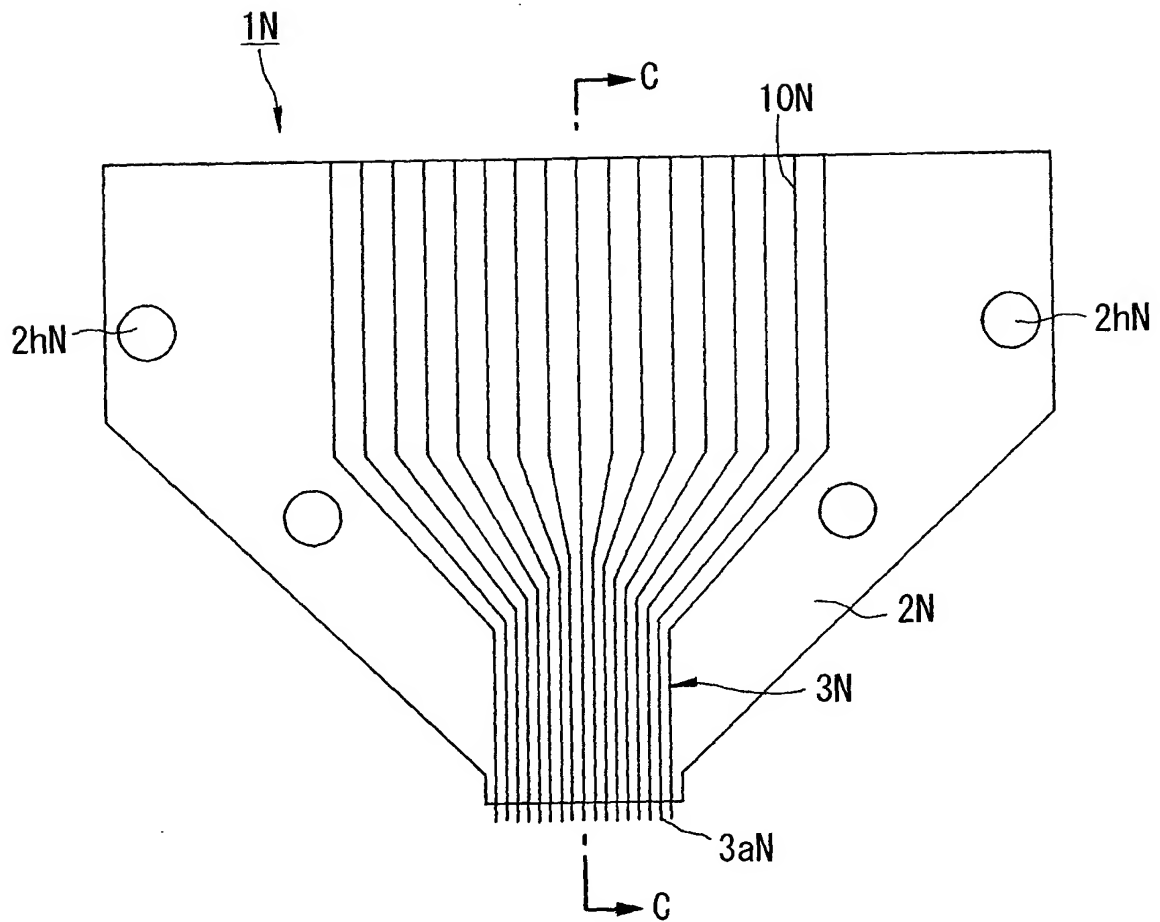
206T90" 805/00T

FIG. 103



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FIG. 104



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FIG. 105

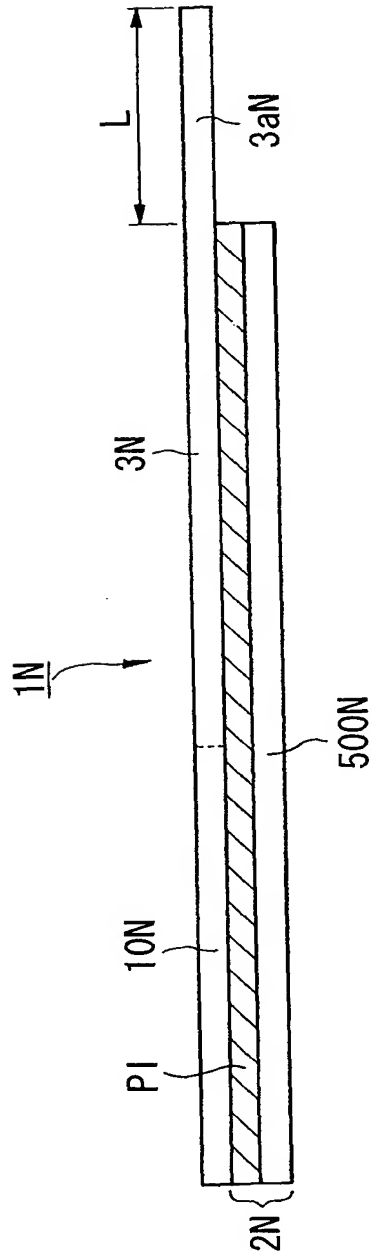


FIG. 106

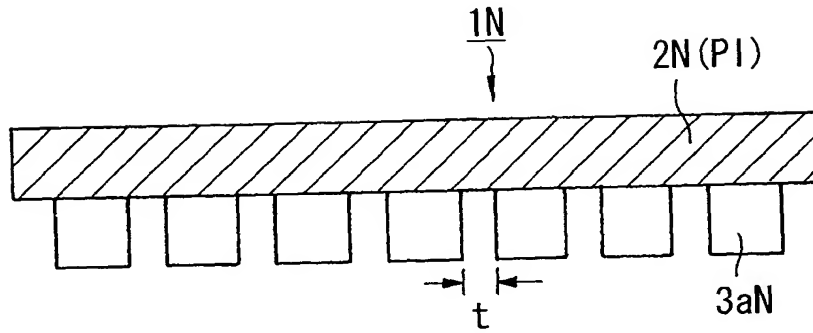
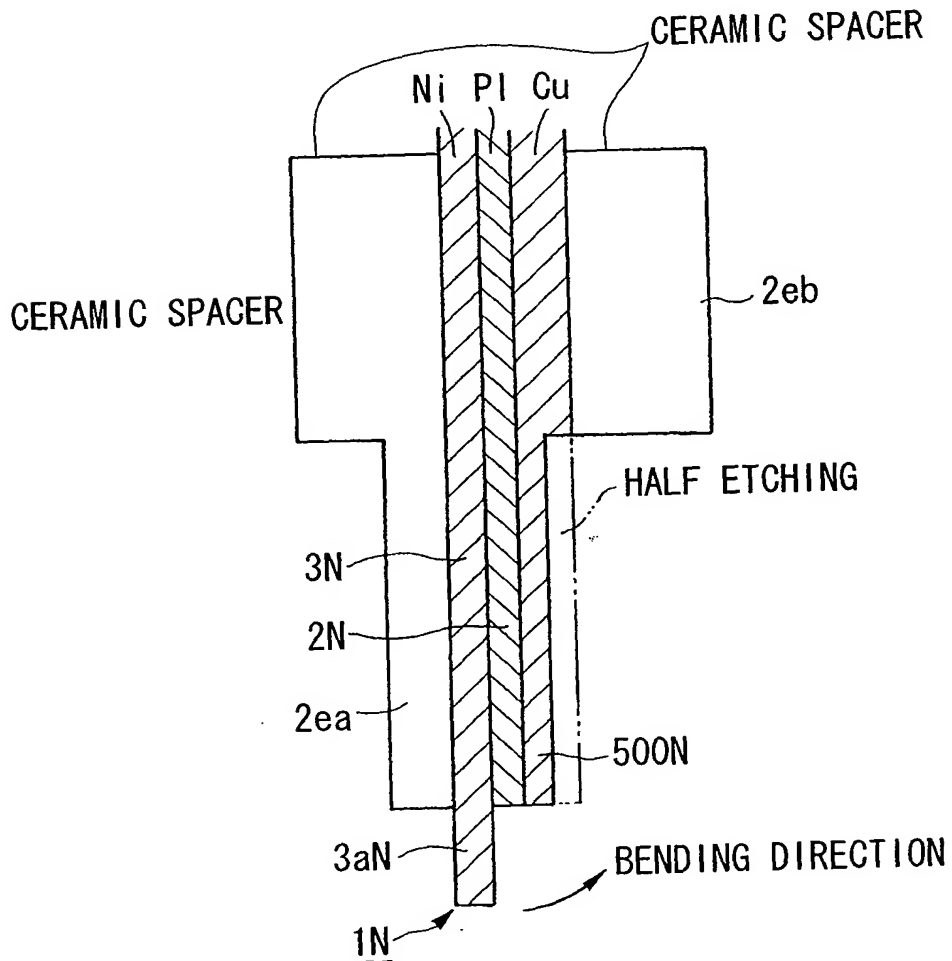


FIG. 107



206T90-8059/00F

FIG. 108

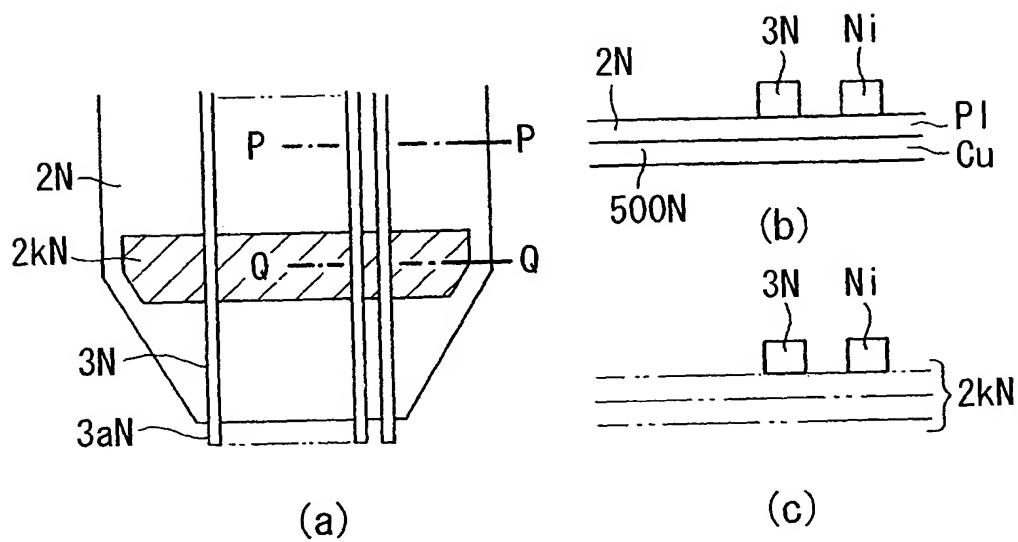


FIG. 109

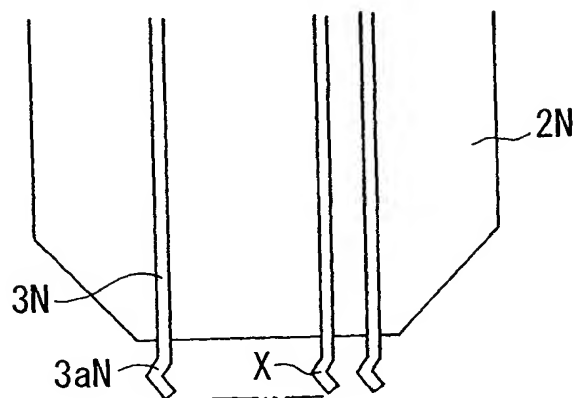
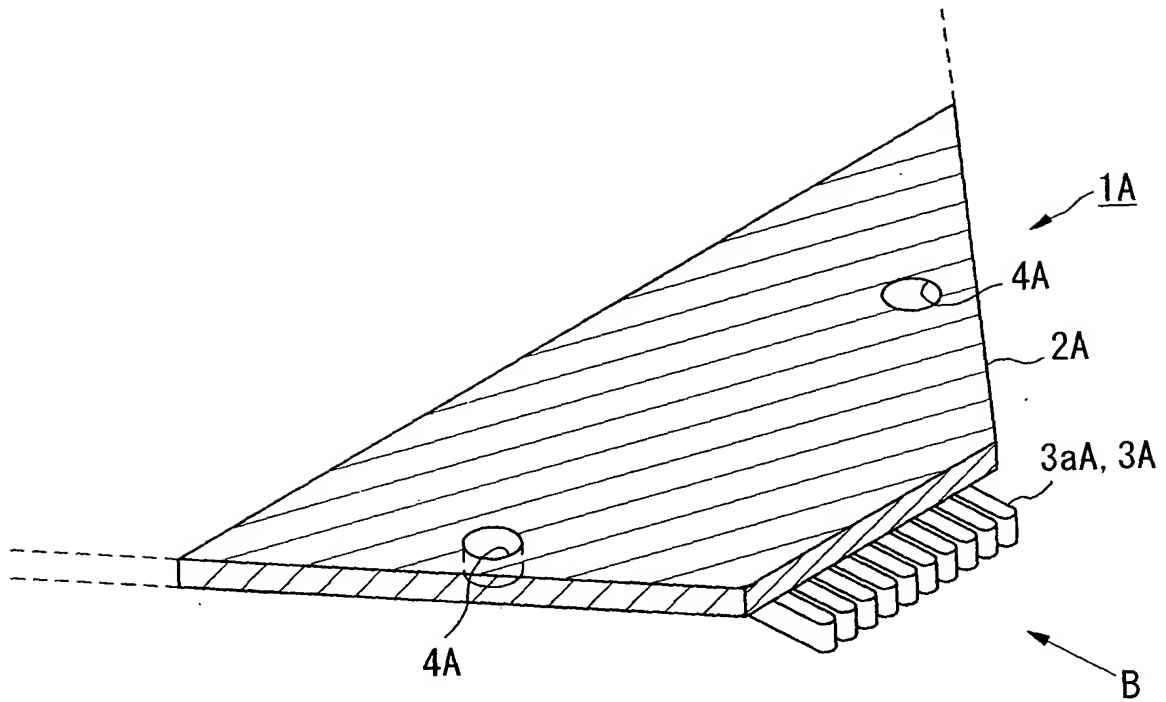
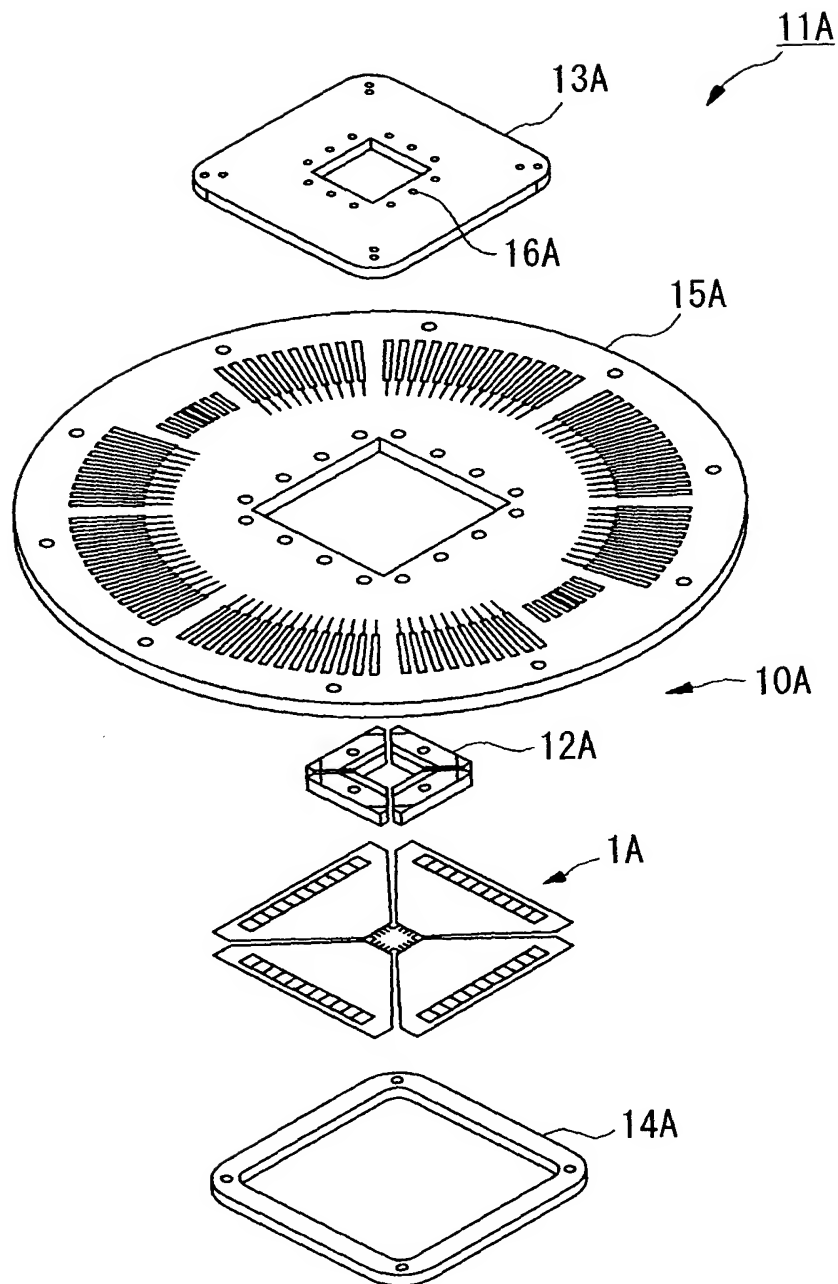


FIG. 110



10076508-051902

FIG. 111



206T90" 8059/00T



FIG. 112

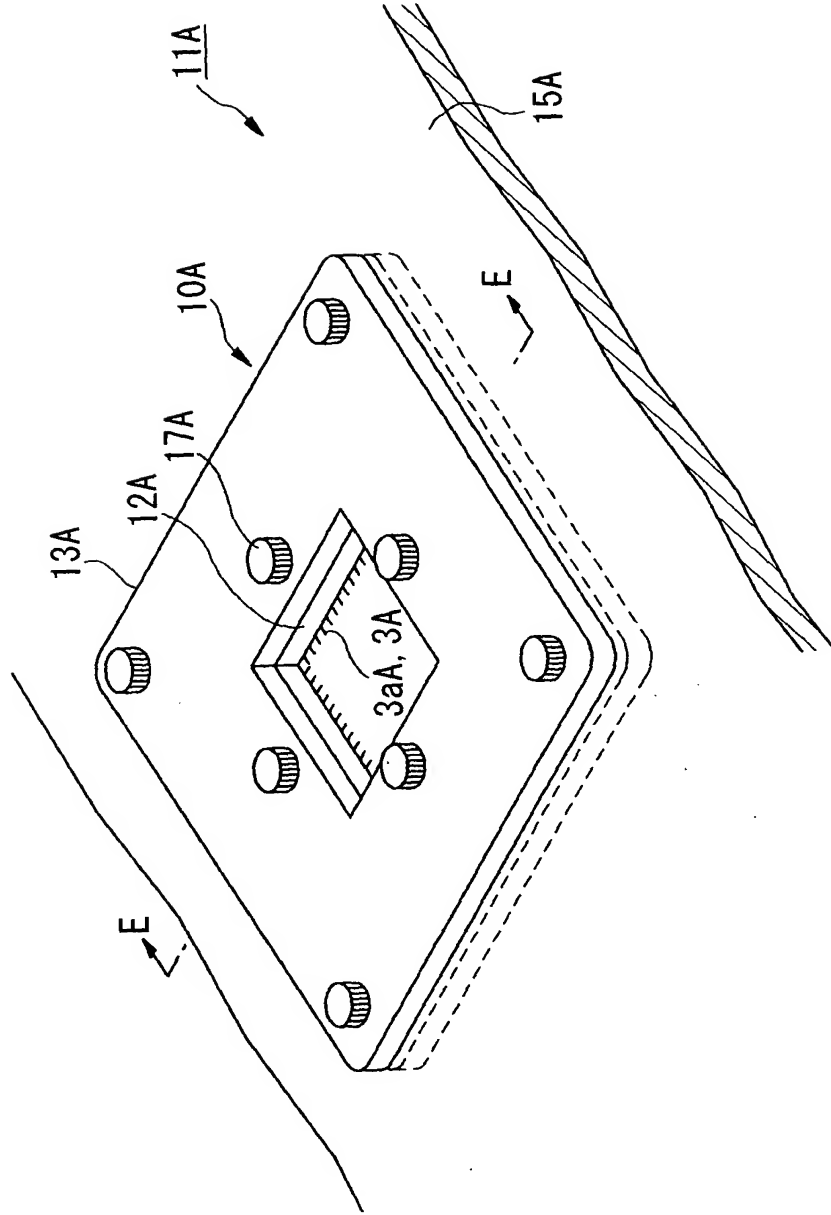


FIG. 113

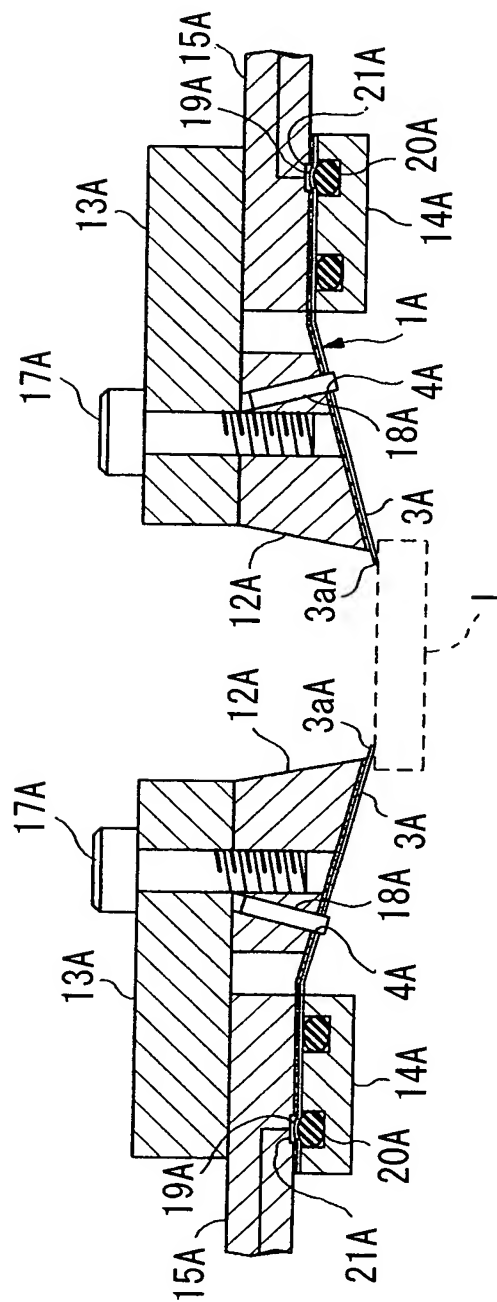
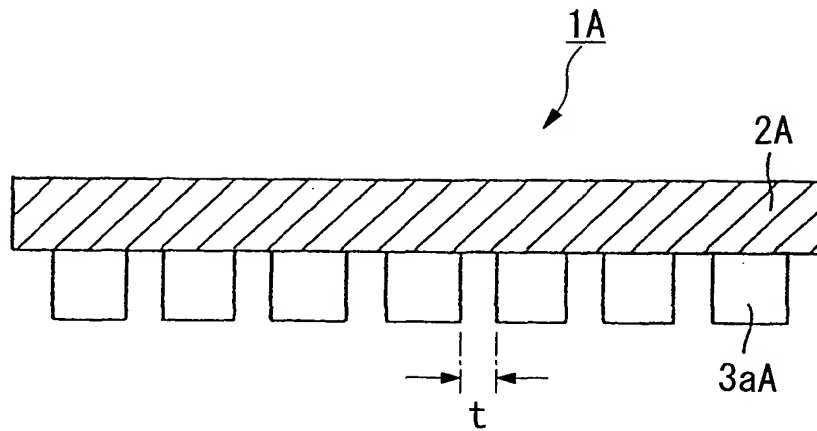
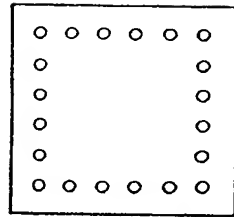


FIG. 114

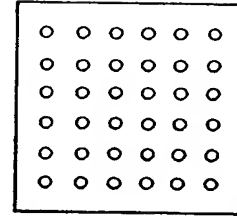


206F50" B059/00F

FIG. 115



PERIPHERALLY ARRANGED  
TERMINALS



PLANARLY ARRANGED  
TERMINALS

(a)

(b)

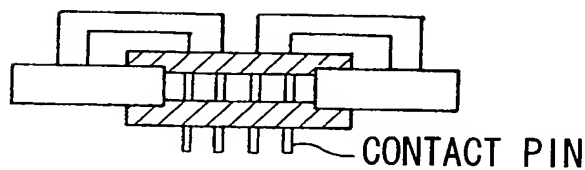
ARRANGEMENT OF ELECTRODE TERMINALS

FIG. 116



HORIZONTAL NEEDLE TYPE PROBE CARD

FIG. 117



VERTICAL NEEDLE TYPE PROBE CARD

10076508-051902